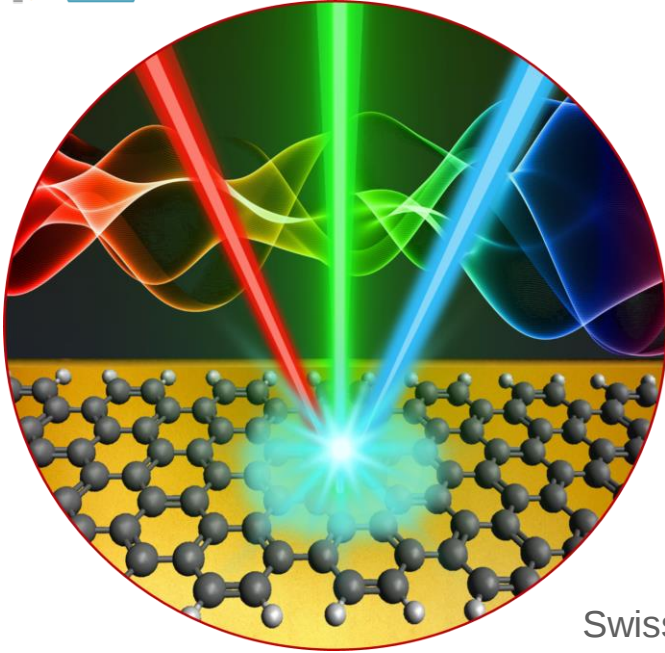




**Nanomaterials
Spectroscopy
and Imaging**



Raman spectroscopy tutorial

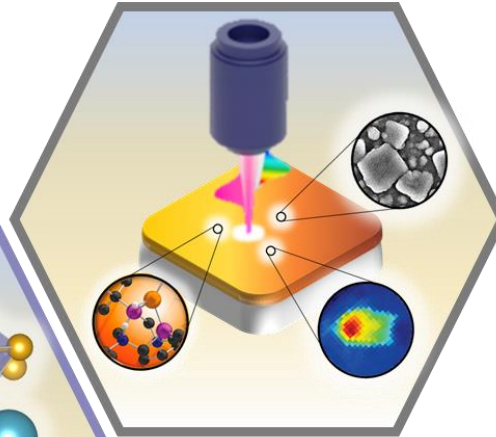
Mirjana Dimitrievska

Transport at Nanoscale Interfaces Laboratory

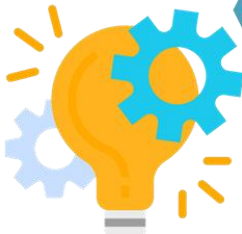
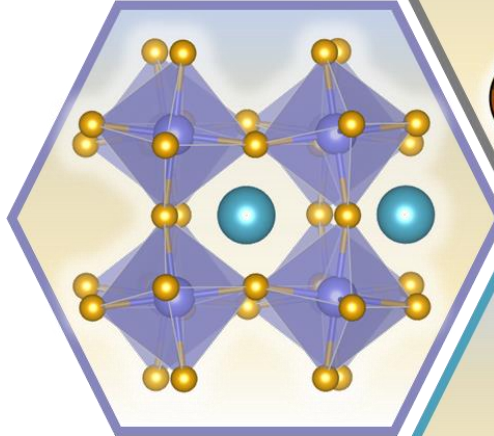
Swiss Federal Laboratories for Material Science and Technology (EMPA)

Switzerland

Spectroscopy



Materials



Nanomaterials Spectroscopy and Imaging

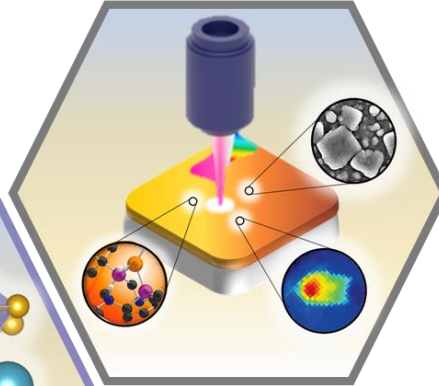


Imaging

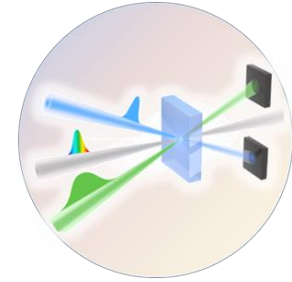
(405) Transport at Nanoscale Interfaces

Nanomaterials Spectroscopy and Imaging Group

Spectroscopy

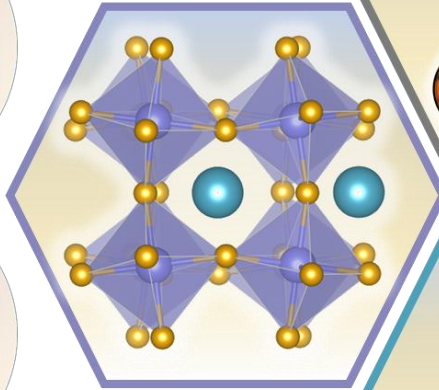


**Raman,
Photo-
luminescence,
Terahertz**



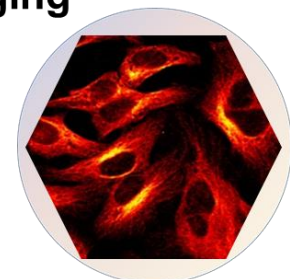
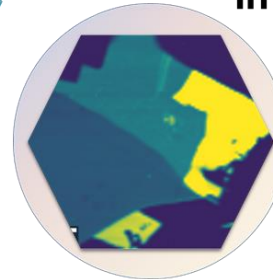
**Time-resolved
spectroscopy,
Stimulated Raman
spectroscopy**

Materials

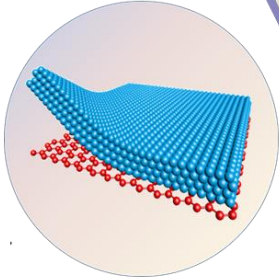
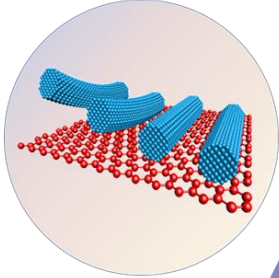


Imaging

**Nanoscale label free
imaging**

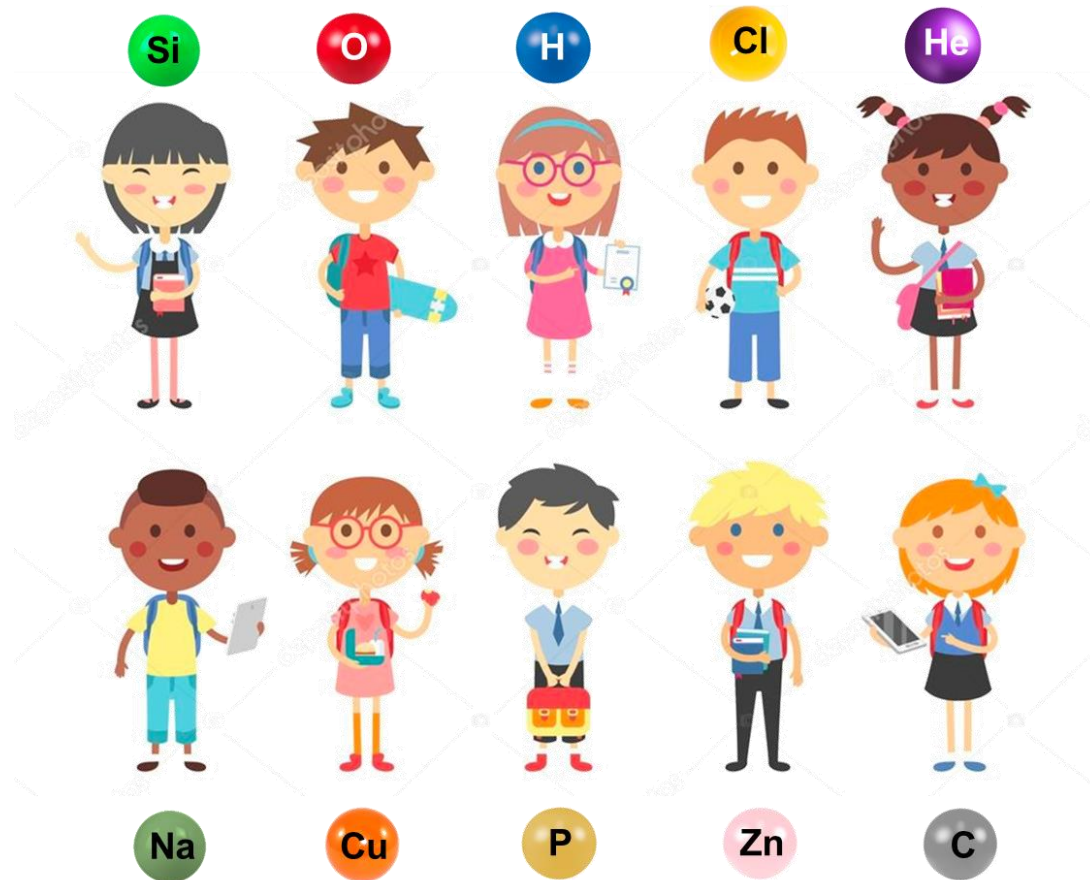


1D-2D



Thin films

Let's start with atoms!

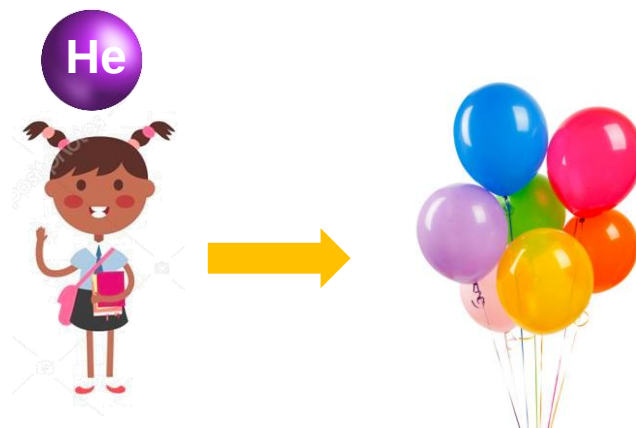
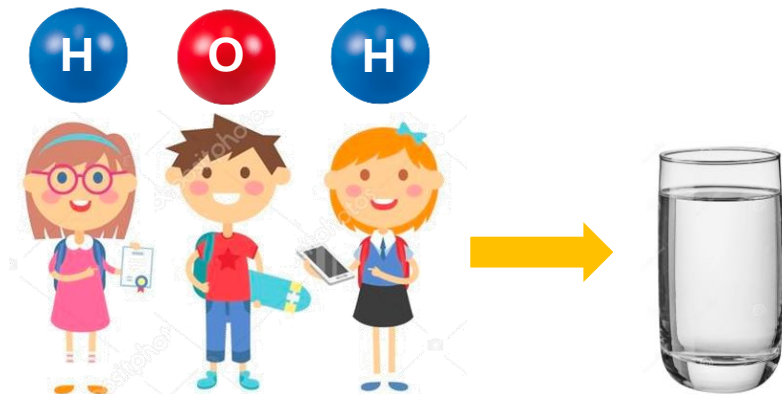
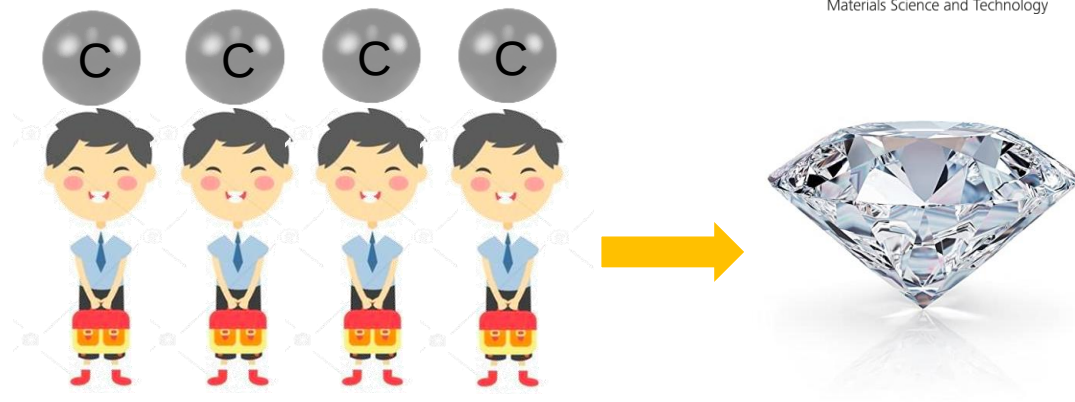
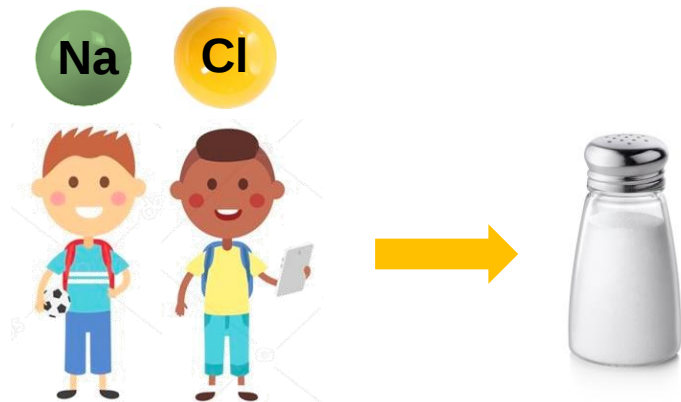


Atoms

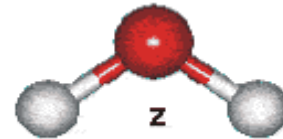
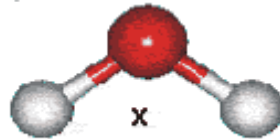
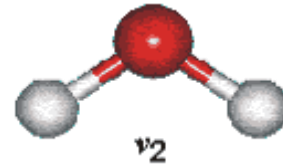
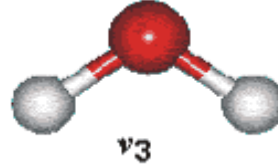
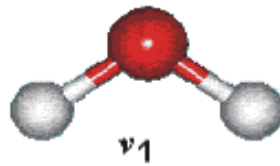


People

(most) Atoms like to bond!



Atoms like to dance!



What can we learn from dancing?



Hawaii



Japan



Portugal

What can we learn from dancing?



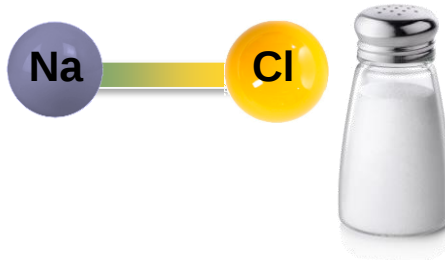
Breakdance



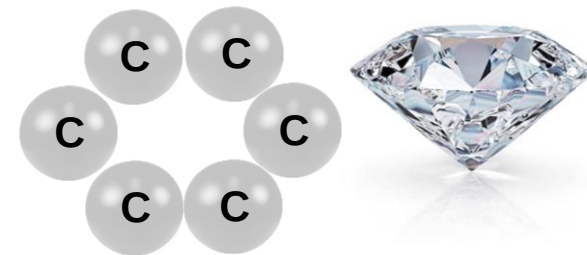
M. Dimitrievska,
Workshop “Dancing with molecules”



Valcer



Tango



What is Raman spectroscopy?

M. Dimitrievska,

Workshop "Dancing with molecules"

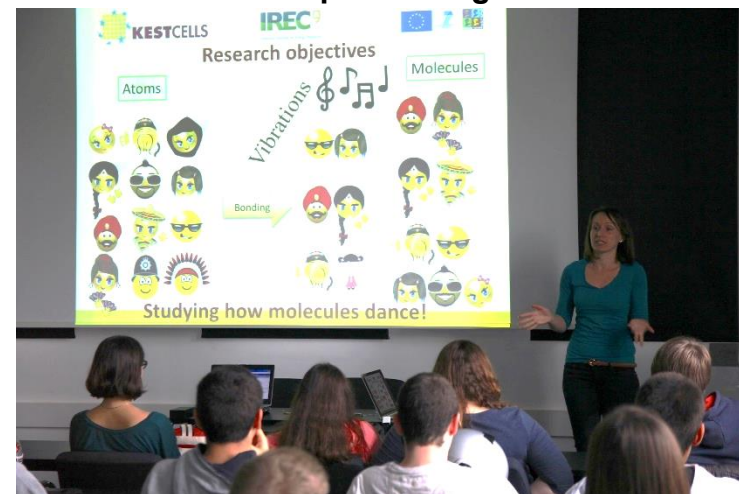
Type

**S****Mo****Cu**

Bonding

**Si****Zn-S****Zn-Se**

Mass

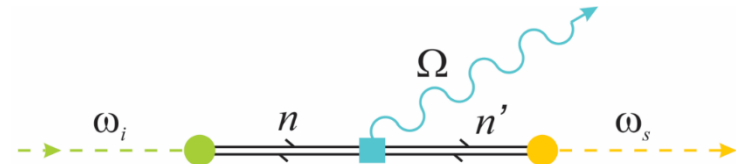
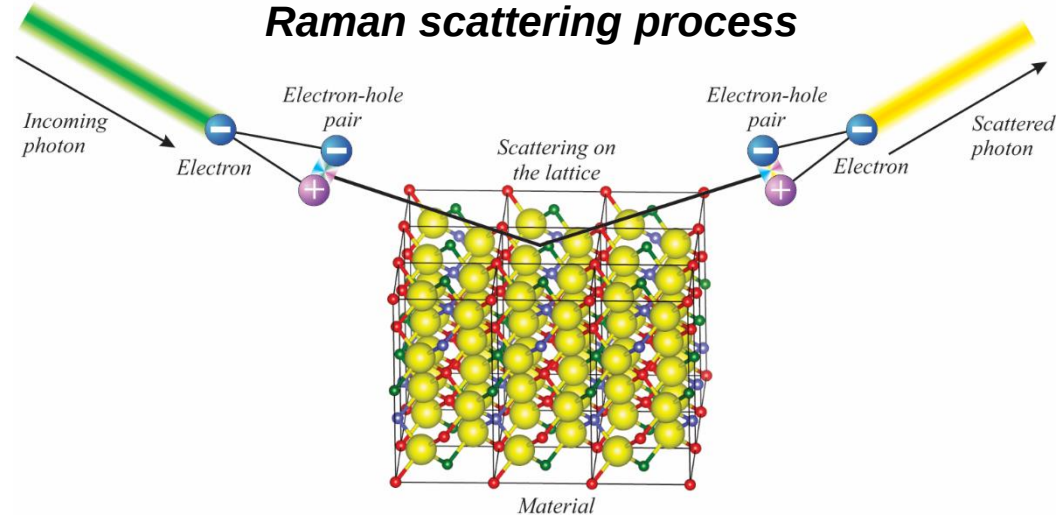
**C****Si****Se**

(most) Atoms (just like people) like to bond!

**Raman spectroscopy:
studying how molecules dance!**

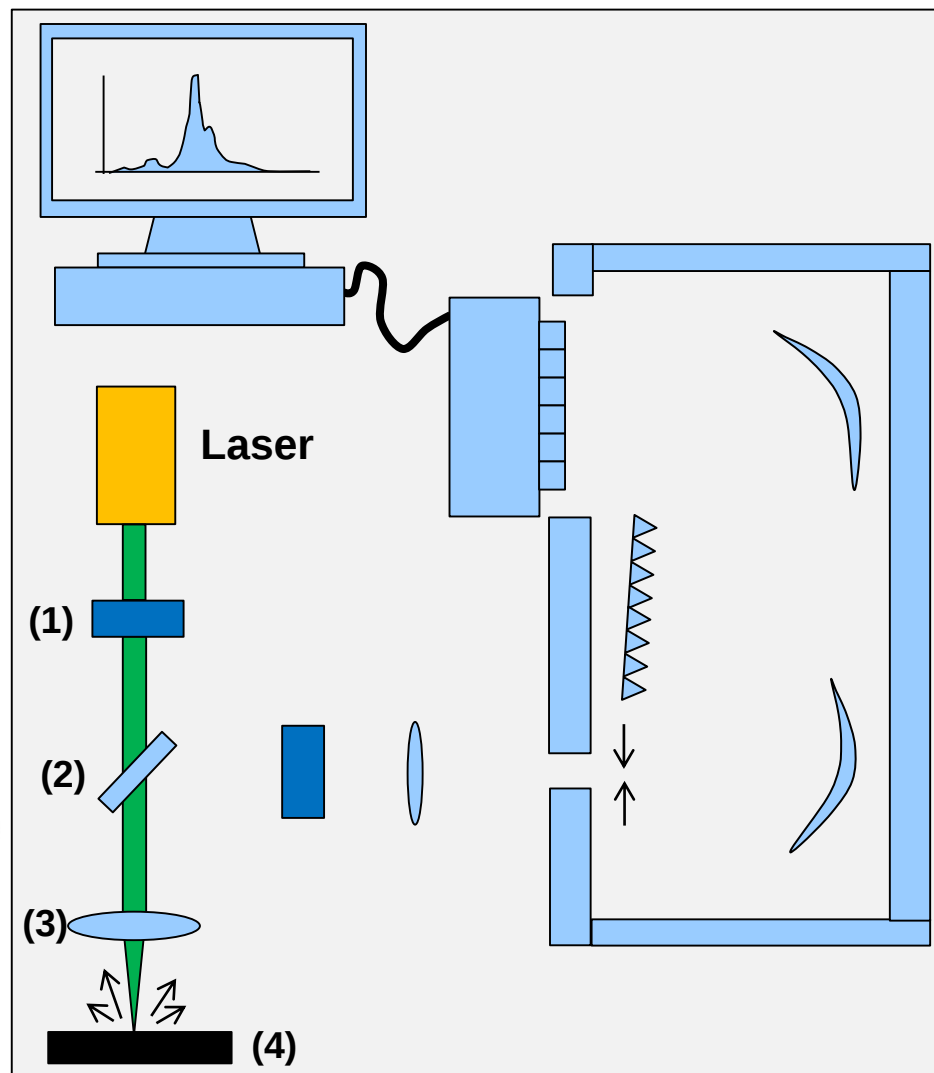


**Raman
instrument**

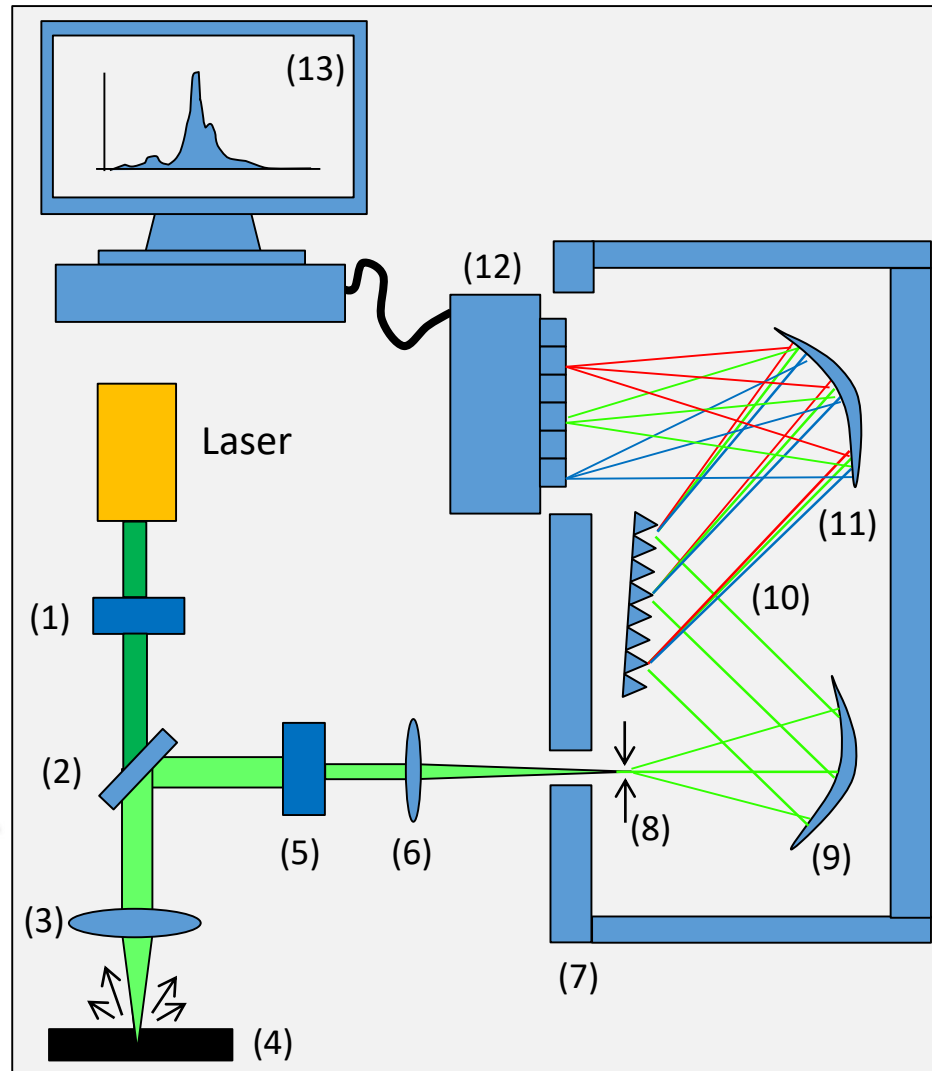


Feynman's diagram

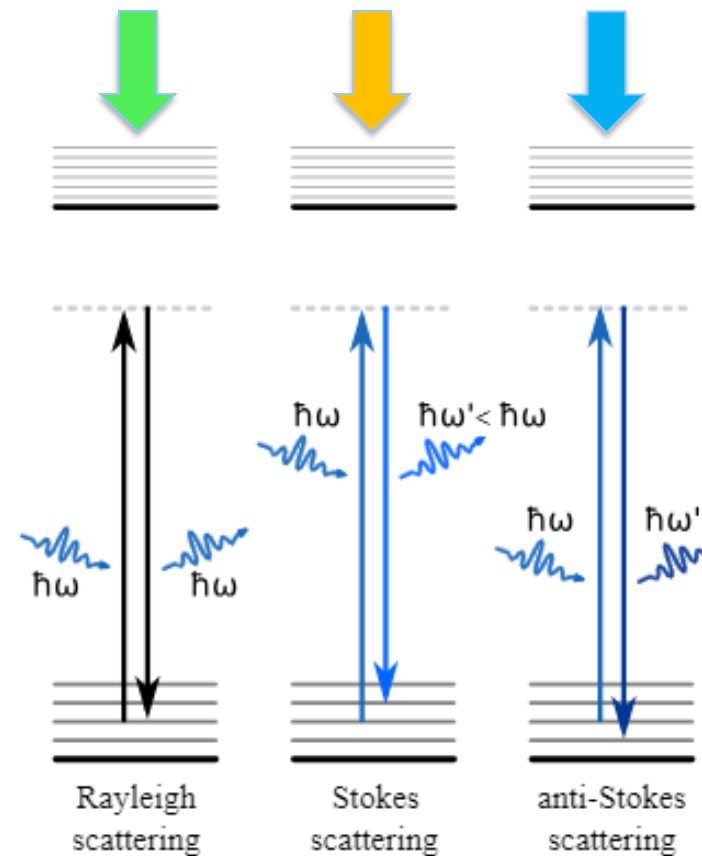
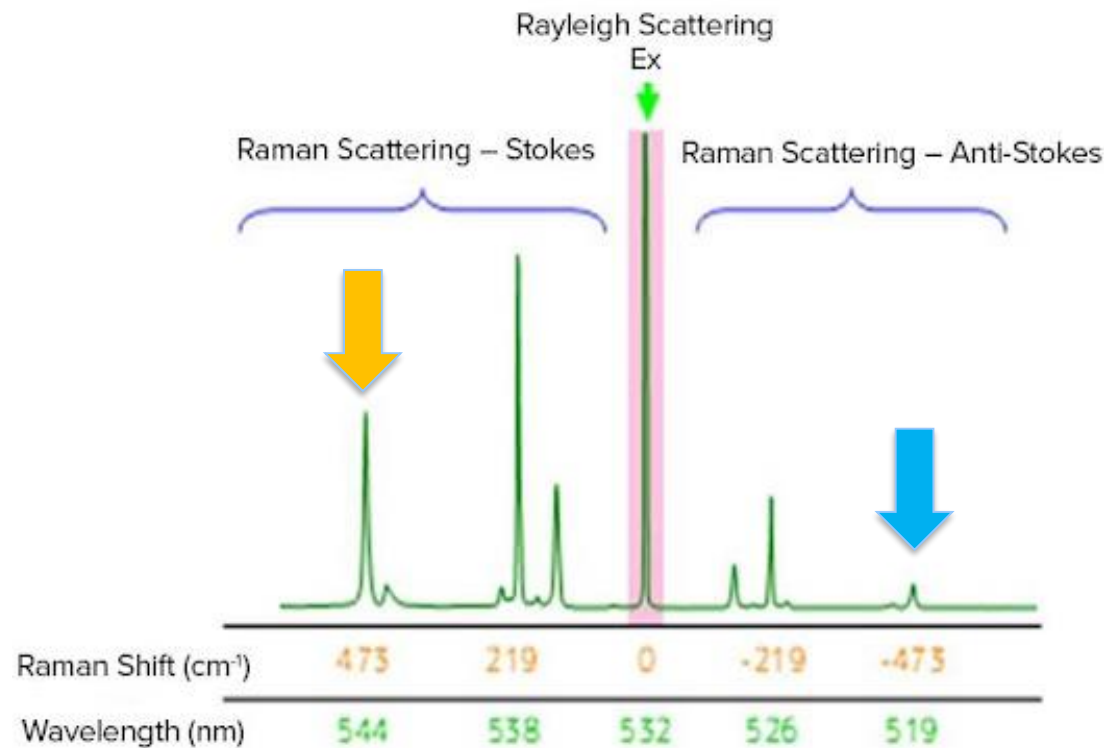
Raman spectroscopy system



Raman spectroscopy system



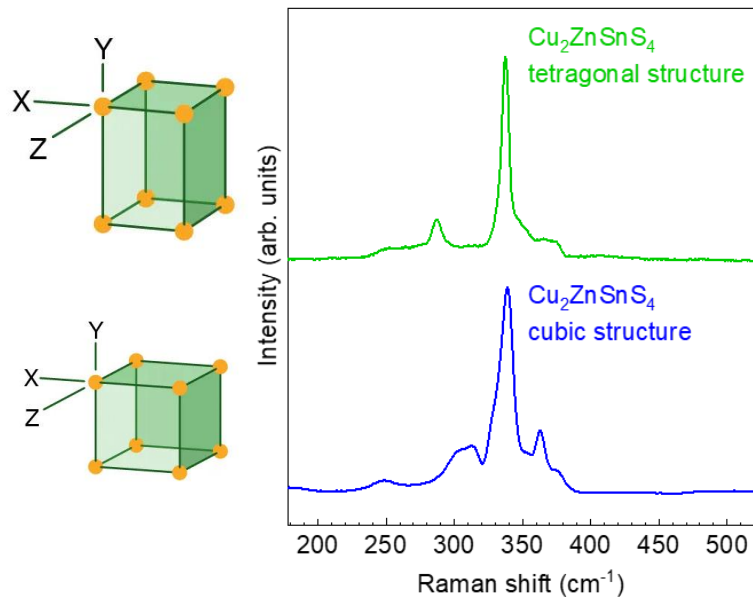
Introduction: Raman spectrum



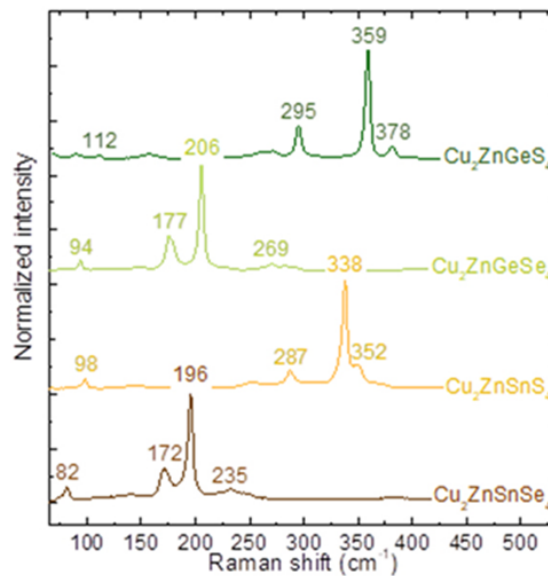
Introduction: Raman spectrum

Raman spectrum provides indirect information about the energy of phonons created or annihilated in the scattering medium. Each spectrum is **a characteristic fingerprint** of the compound and contains information about:

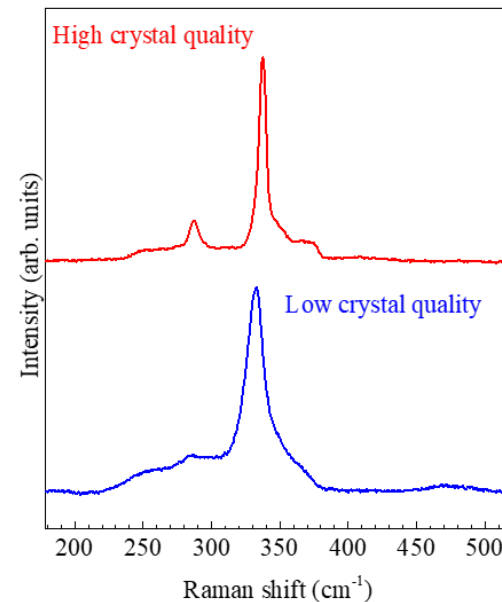
Crystal structure



Atomic Composition



Crystal quality



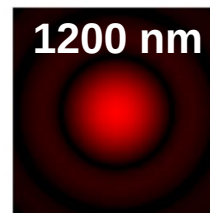
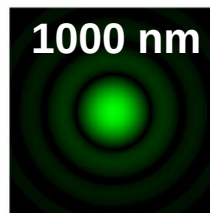
Introduction: Raman spectroscopy

An ideal characterization tool for obtaining deeper insights about fundamental properties which is **simple** and **non-destructive**, offers **high resolution**, gives **structural and chemical information**, and is **applicable** at both **laboratory and mass-production scales**.

Non-destructive



High resolution (laser spot size)



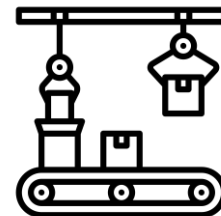
Fast



Structural and chemical information



Lab and industrial scales



How to do measurements?

Considerations to take into account when performing the measurements:

- ☐ **Excitation energy (laser wavelength)**
- ☐ **Power density and signal/noise ratio**
- ☐ **System alignment and calibration**

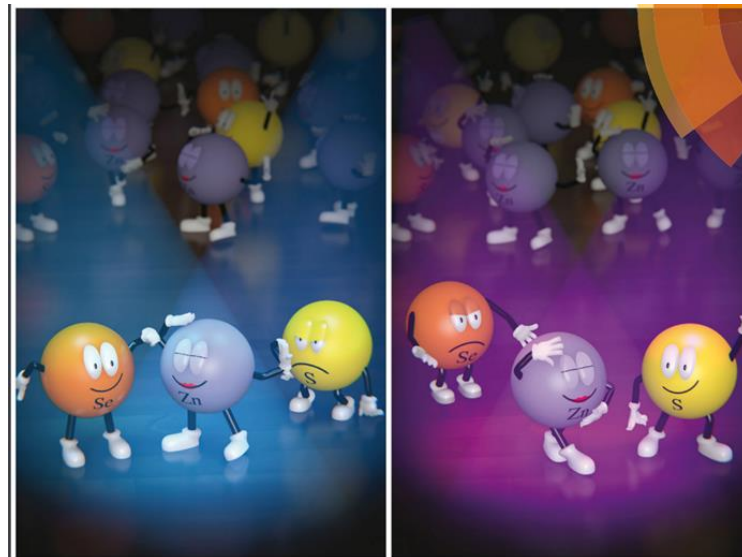
Excitation energy (laser wavelength)

Music



Laser wavelength =
Different types of music

Light



Excitation energy (laser wavelength)



ISSN 1463-9076



PAPER
M. Dimitrievska, V. Inquarto-Roca et al.
Resonant Raman scattering of $\text{ZnS}_x\text{Se}_{1-x}$ solid solutions: the role of S and Se electronic states

175
YEARS

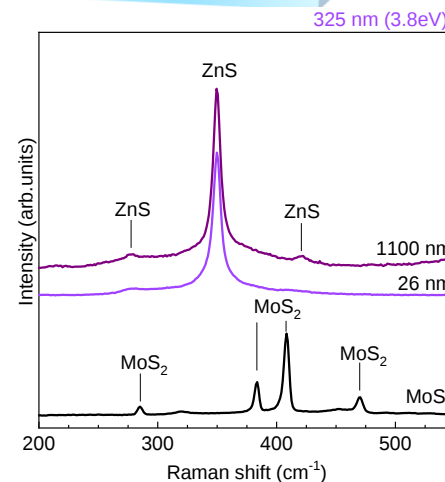
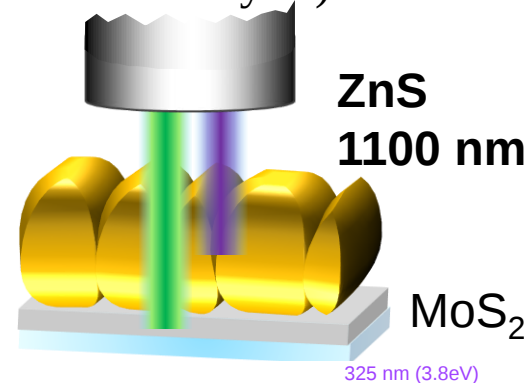
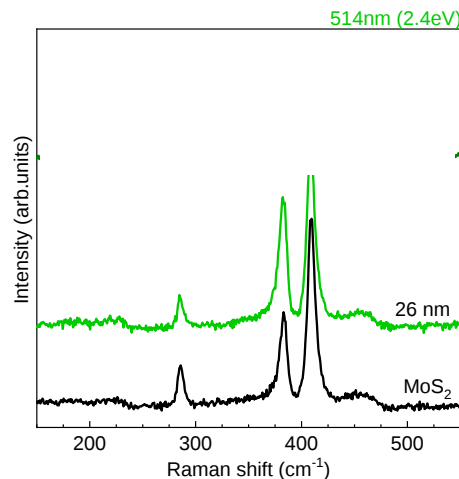
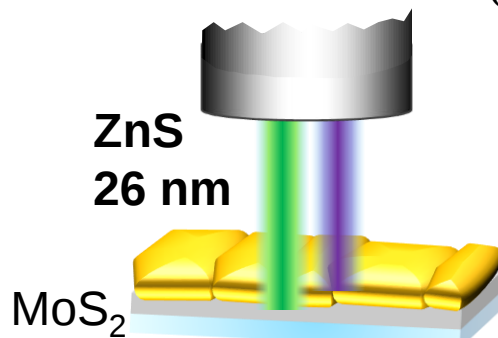
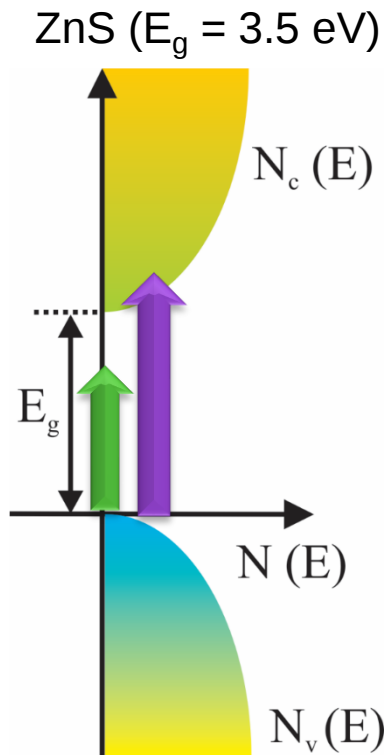
**M. Dimitrievska, *Phys. Chem. Chem. Phys.*,
2016,18, 7632-7640**

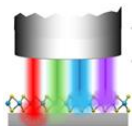
**Resonant Raman scattering of
 $\text{ZnS}_x\text{Se}_{1-x}$ solid solutions: the role of S and
Se electronic states**

Excitation energy (laser wavelength)

$\lambda_{ext} > E_g$: **strong** photon-matter interaction
 (low penetration and small volume analysis)

$\lambda_{ext} < E_g$: **weak** photon-matter interaction
 (larger volume analysis)





Multiwavelength excitation Raman spectroscopy

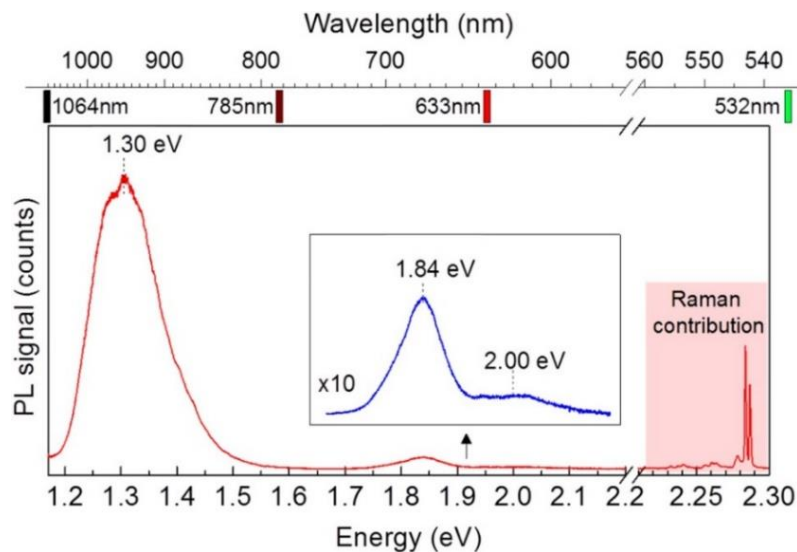


Materials Science and Technology

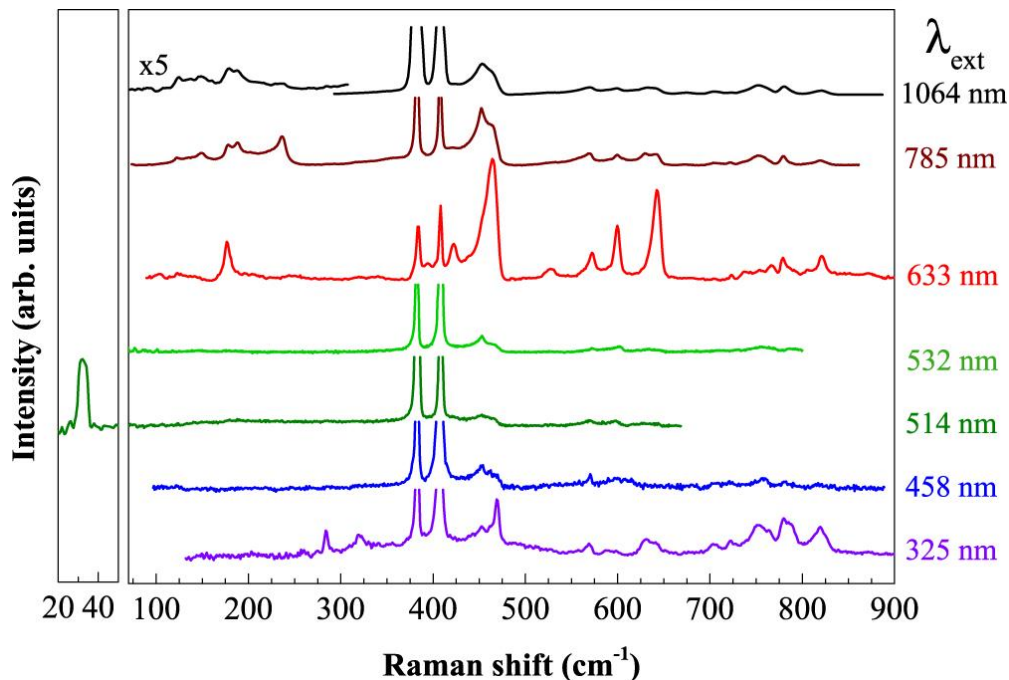
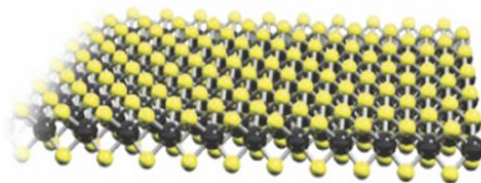
$\lambda_{\text{ext}} \approx E_g \text{ or } E_i$: resonance conditions

Raman intensity:

$$I \propto \frac{2\pi}{\hbar} \left| \frac{\langle 0 | H_{e-r} | n \rangle \langle n | H_{e-ph} | n' \rangle \langle n' | H_{e-r} | 0 \rangle}{(\hbar\omega_i - (E_{|n\rangle} - E_{|0\rangle}) + i\Gamma)(\hbar\omega_s - (E_{|n'\rangle} - E_{|0\rangle}) + i\Gamma)} \right|^2$$

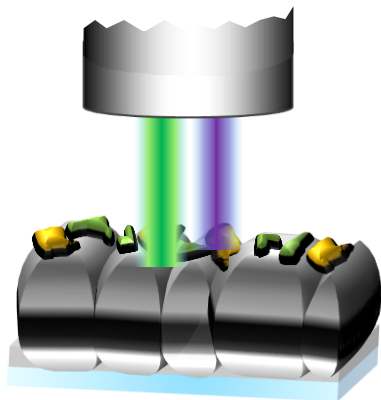


MoS₂
(single crystal)

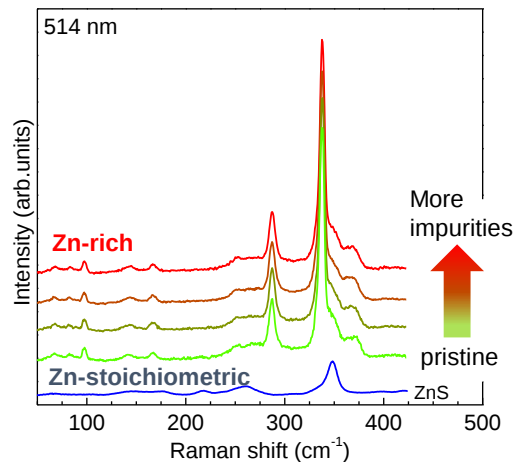


Multiwavelength excitation Raman spectroscopy: impurity identification

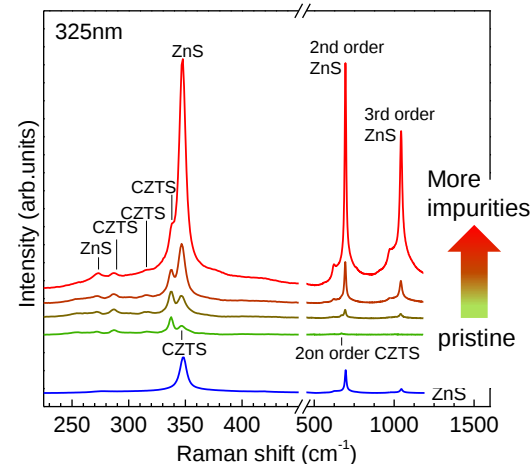
Assessment of ZnS in $\text{Cu}_2\text{ZnSnS}_4$



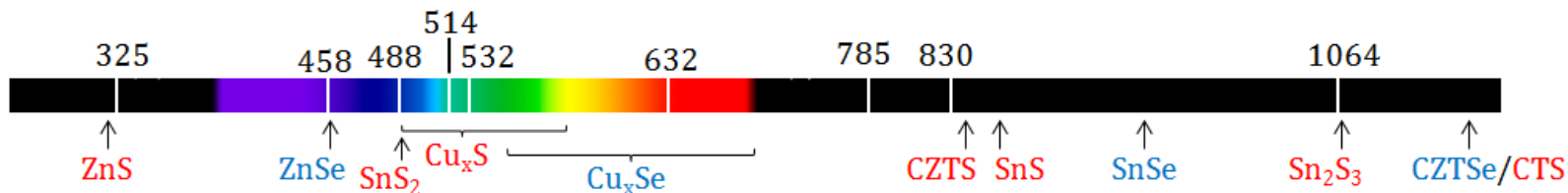
Standard Raman spectroscopy



Resonance Raman spectroscopy

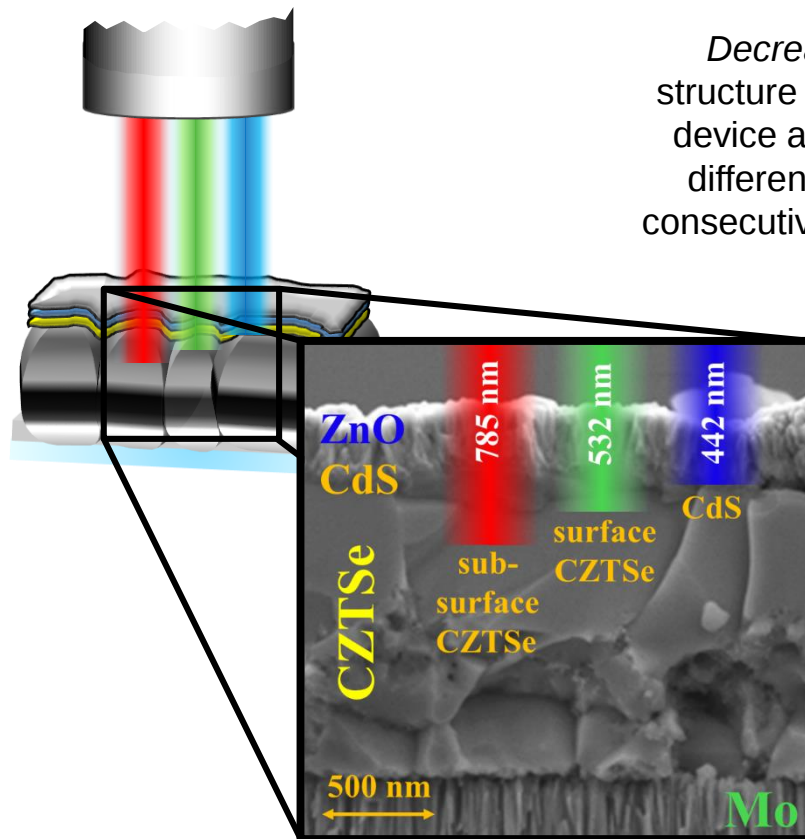


Multiwavelength excitation Raman spectroscopy

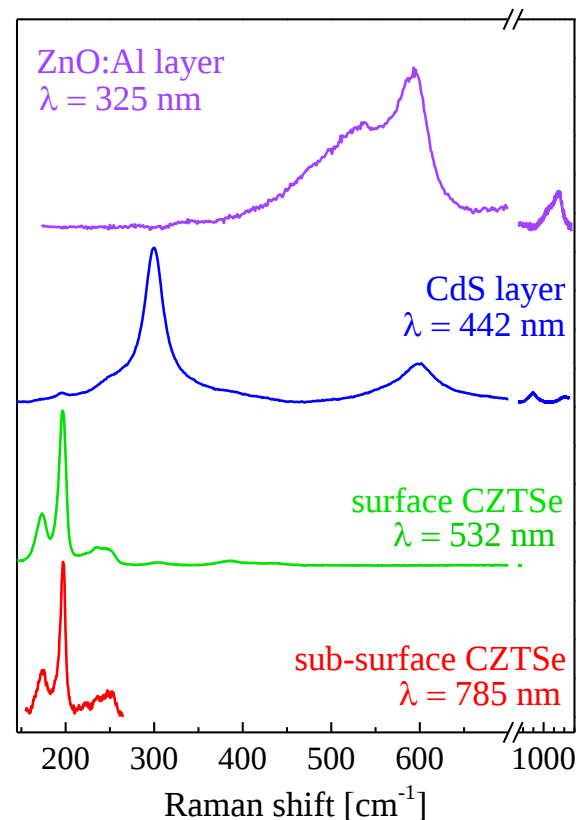


Excitation energy: application

In-depth non-destructive characterization of layered devices



Decreasing band gap structure of the solar cell device allows analyzing different layers using a consecutive *lower energy excitation*.

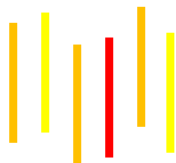


Applied power density

Raman spectroscopy is a **non-destructive technique**, but this is only **within certain limits**.

The irradiance of the sun is around $0.1\text{W}/\text{cm}^2$.

If we focus a laser beam of **1 mW** through a microscope on a spot of **1 μm** diameter, then the obtained density of power is **5 orders of magnitude higher** than that of the Sun.



$\approx 0.1\text{W}/\text{cm}^2$



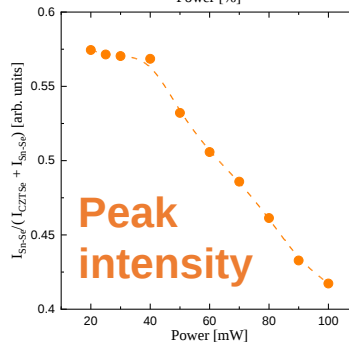
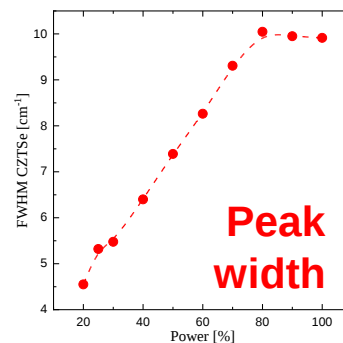
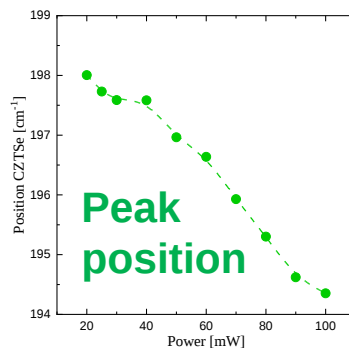
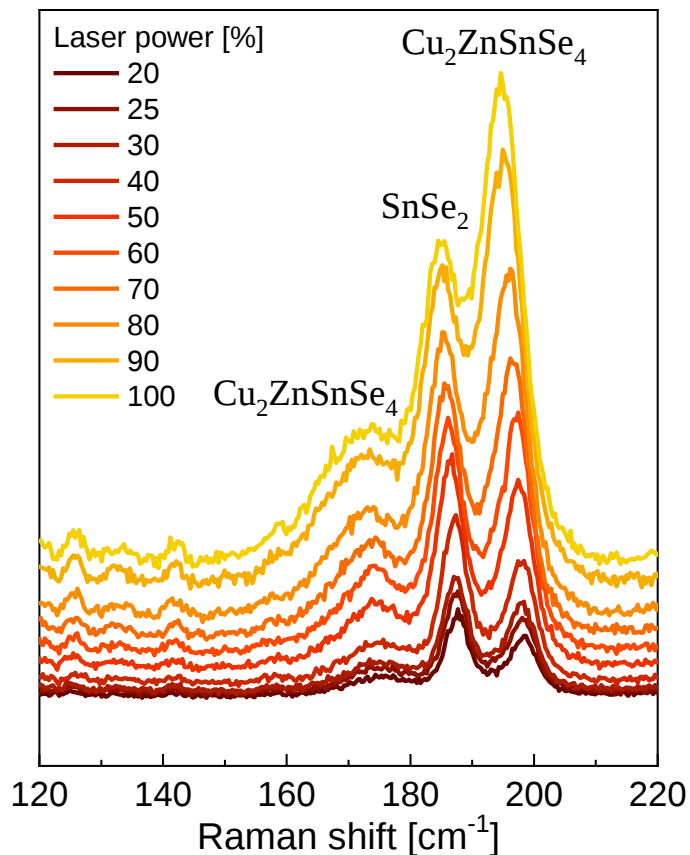
1mW

Diameter 1 μm

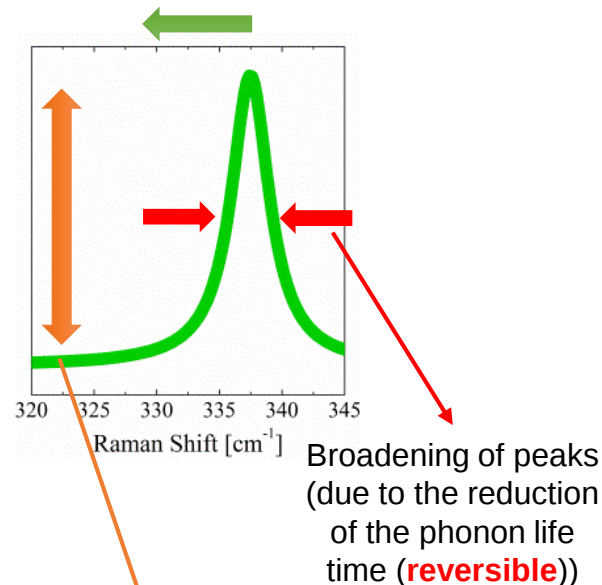
$\approx 63600\text{W}/\text{cm}^2$

Applied power density

Power study



Peak position (due to the expansion of the lattice (**reversible**))



Change of the shape, intensity, or appearance of new peaks (due to recrystallization, decomposition or reaction between the phases (**irreversible**))

Applied power density

Power study recipe

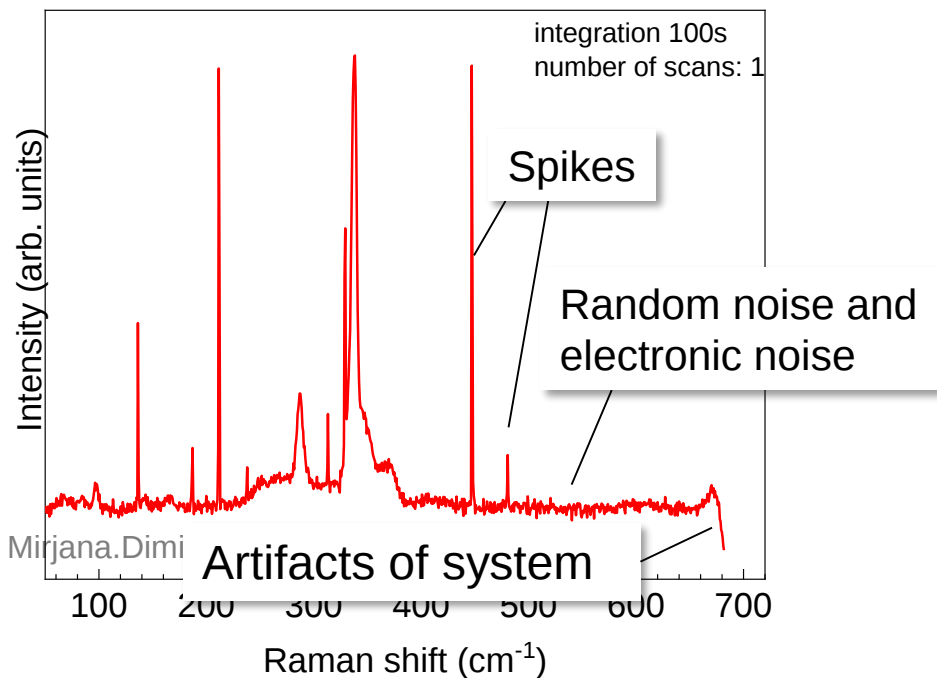
- Start with lowest power
- Measure Raman spectrum (1)
- Increase power for certain increment (don't change the measurement point)
- Measure Raman spectrum (2)
- Reduce power to minimum power
- Measure Raman spectrum (3)
- Compare (1) and (3) spectrum  **Decision point**
- Increase power for certain increment (don't change the measurement point)
- Measure Raman spectrum (4)
- Compare (1) and (4) spectrum  **Decision point**
- Increase power for certain increment (don't change the measurement point)
- Measure Raman spectrum (5)
- Compare (1) and (5) spectrum  **Decision point**
-

Decision point: If you see differences between the spectra, go back to lower power, and do all measurements with that power. If no differences, increase power.

Signal/noise ratio

Low power density could induce small signal/noise ratio (SNR) that could make the interpretation of the Raman measurements more difficult.

There are **different types of noise**. Depending on their origin they can be reduced/solved or not.



Spike: originated from cosmic rays. The probability of occurrence increases with time acquisition

Random noise: intrinsic to measurement. It is reduced when the integration time is increased.

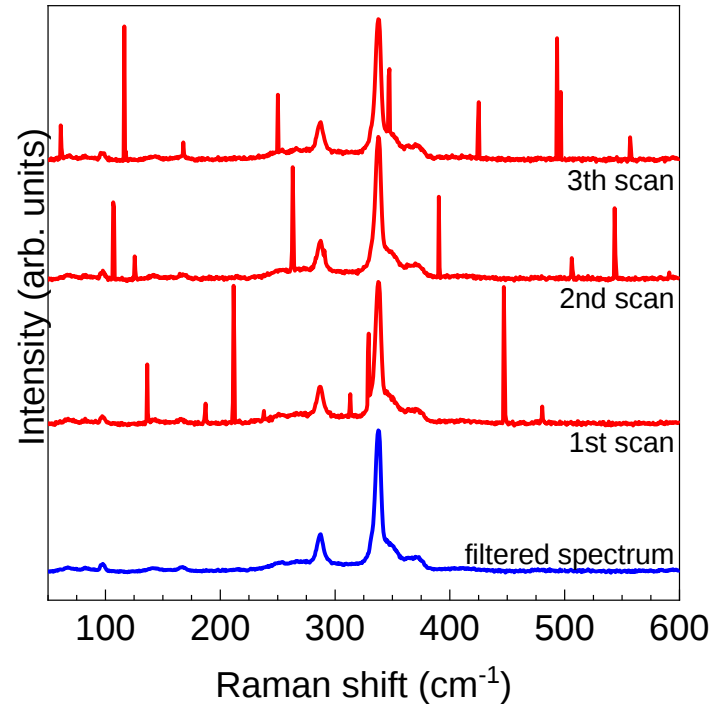
Electronic noise: intrinsic - depends on the detector. It limits the SNR of the system.

Artifacts of the system: intrinsic – depends of the optical system. It doesn't change with the integration time.

Signal/noise ratio

Different strategies could be utilized for the reduction of these effects:

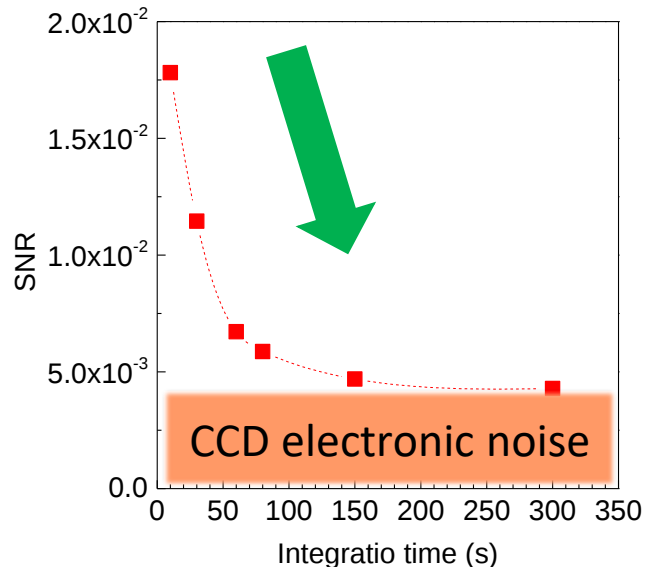
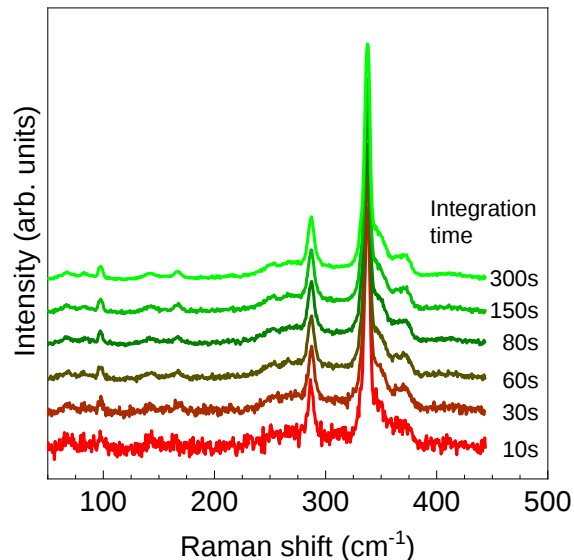
Spikes: elimination of spikes can be obtained comparing different scans and making the average spectra after cleaning up the spikes



Signal/noise ratio

Different strategies could be utilized for the reduction of these effects:

Random noise: can be reduced by increasing the time of integration, however this will also cause the increase in the spike occurrence



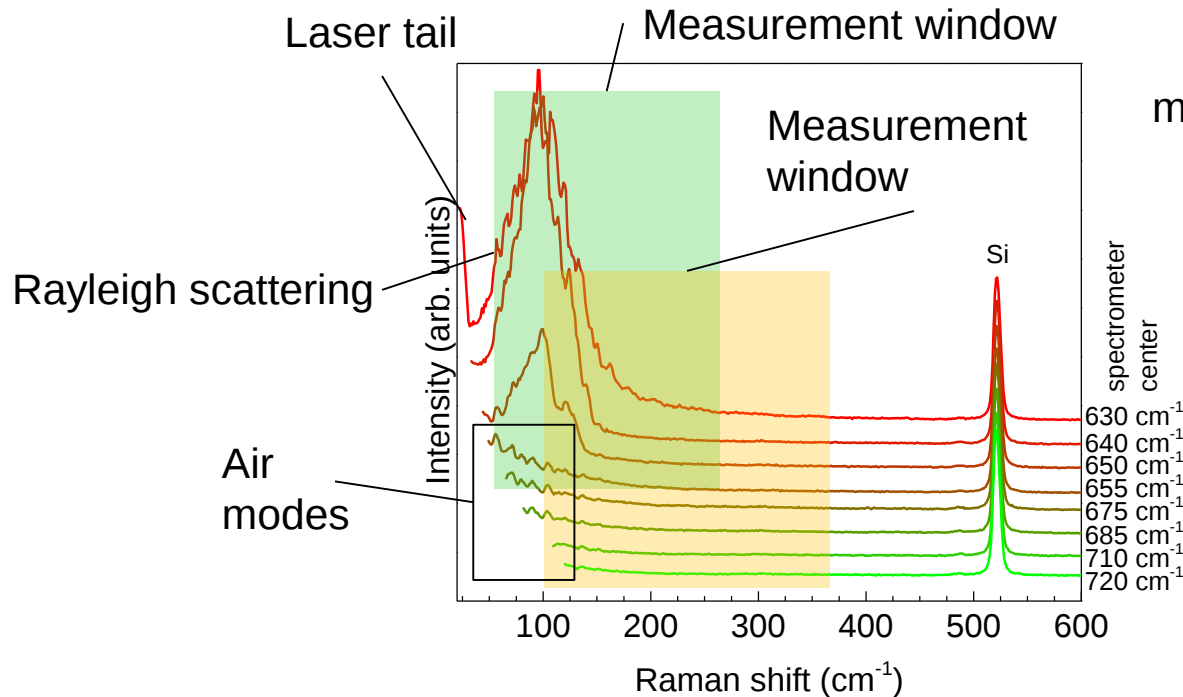
However, **electronic noise** is intrinsic property of the detector. Using detectors with lower working temperature could reduce this effect.

In order to improve the signal/noise ratio, it is necessary to optimize the acquisition conditions, time integration and number of scans!

System alignment

A correct alignment of the optical system is very important in order to optimize the signal/ noise ratio.

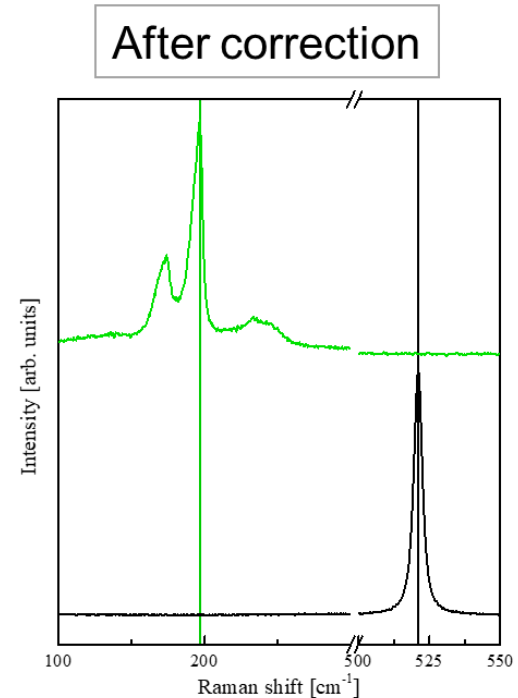
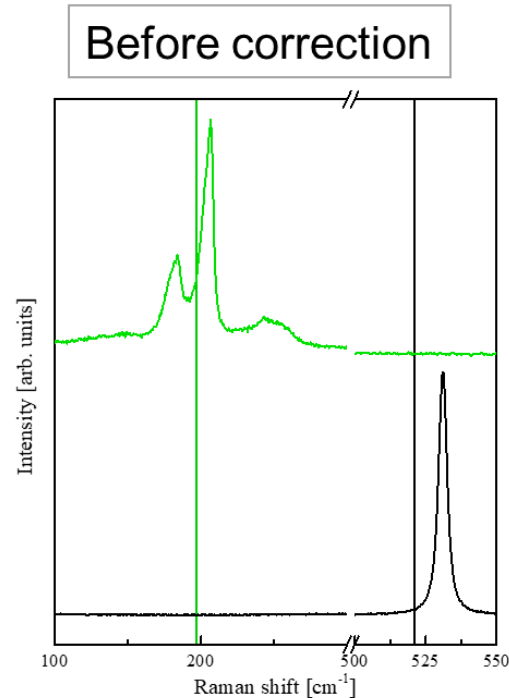
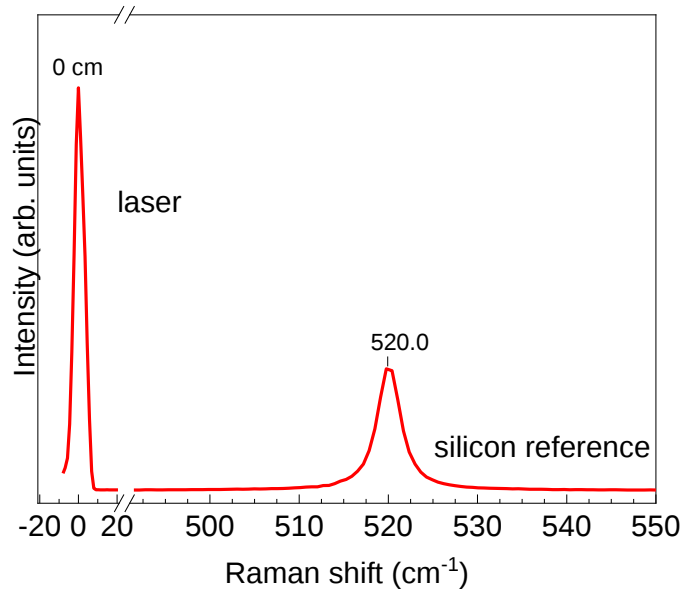
Example:
Moving the
measured spectral
window



System alignment

Finally, a correct calibration of the Raman frequencies is required in order to obtain the correct positions of Raman peaks.

Correct calibration: it is necessary to define the laser position at 0 cm^{-1} . Also, it is necessary to use a reference sample in order to correct the calibration between pixels and wavenumbers. (For example, the silicon, peak position at 520 cm^{-1})

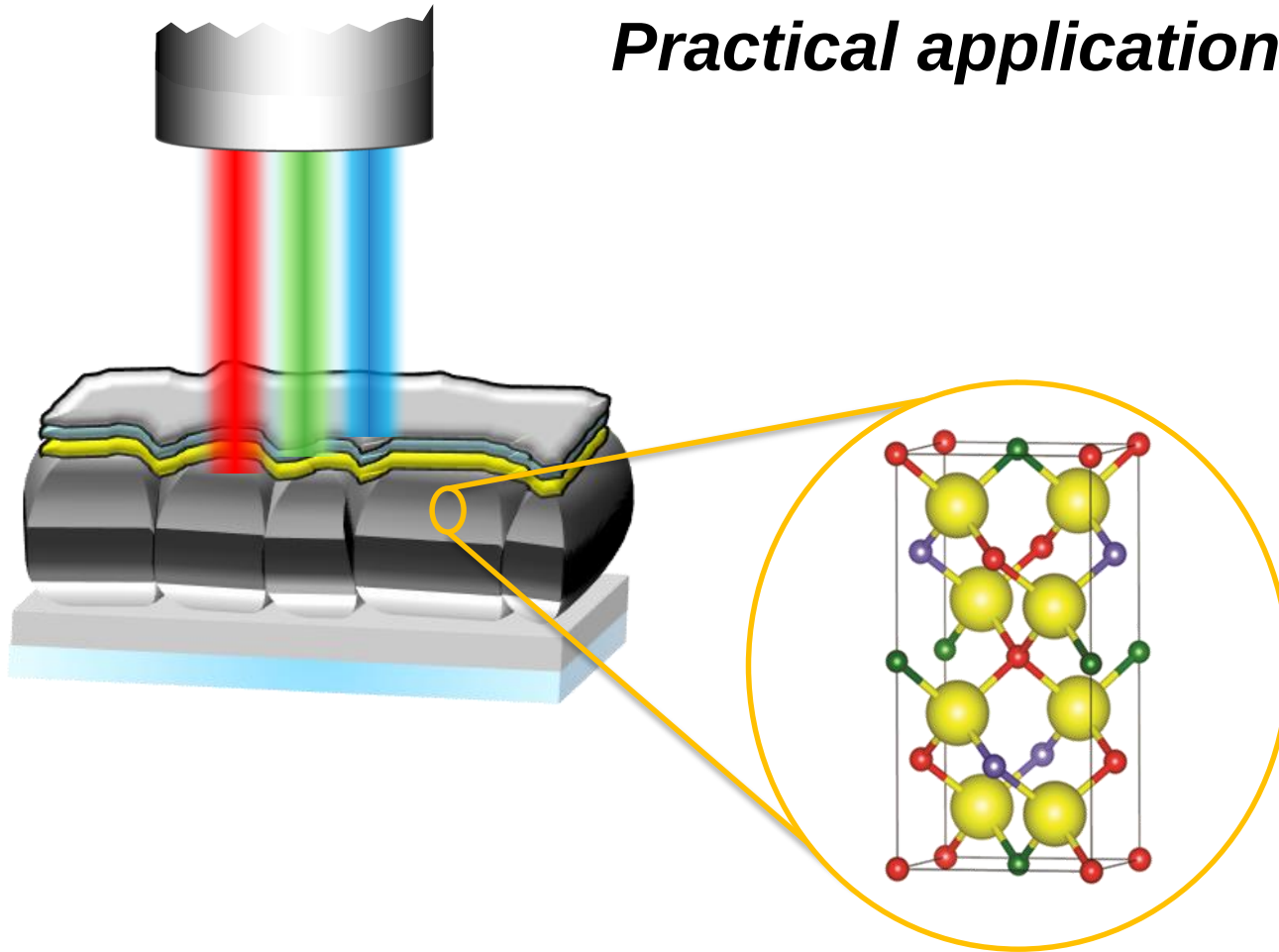


How to do measurements?

Recipe:

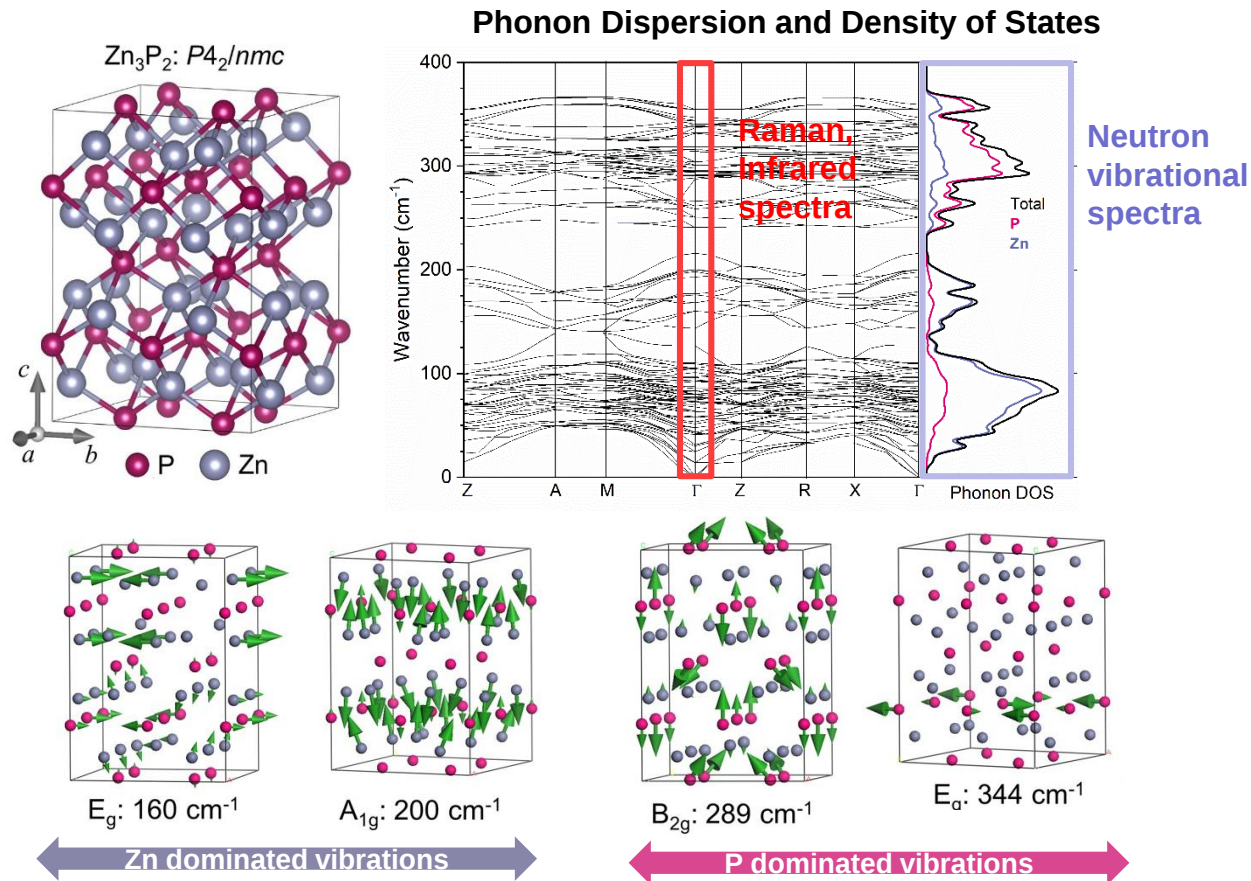
- **Pick the right energy excitation**
 - **Consider material's properties, such as band gap**
 - **What do you need to detect?**
 - **What do you want to investigate?**
- **Do a power study and optimize SNR**
 - **Choose the right power, integration time, and number of scans to obtain the lowest SNR, without damaging the material**
- **Choose the right spectral window for your study**
- **Measure reference samples for calibration of position as often as possible**

Practical application



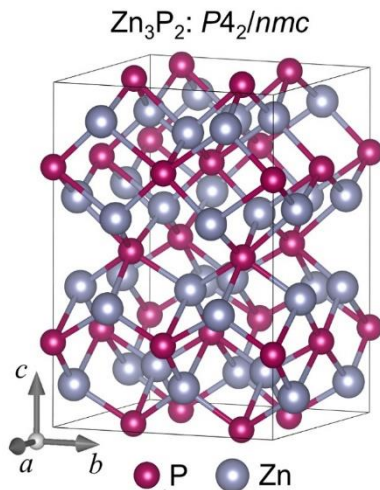
Application: Identification of fundamental modes

Lattice dynamic and structural characterization (DFT and experiment)



Application: Identification of fundamental modes

Identification of Raman mode positions and symmetry type



Irreducible representation for Raman active modes:

$$\Gamma_{\text{Raman}} = 9A_{1g} + 10B_{1g} + 4B_{2g} + 16E_g$$

Labels:

(A, B), E, T : non-, double-, triple- degenerate

A or B : symmetric or asymmetric with respect to the principal symmetry axis C_n

1 or 2 : symmetric or asymmetric with respect to the rotation around a two-fold axis (C_2) normal to the principal symmetry axis C_n

g or u : symmetric or anti-symmetric with respect to the inversion.

$$\mathfrak{R}_{A_{1g}} = \begin{pmatrix} a & 0 & 0 \\ 0 & a & 0 \\ 0 & 0 & b \end{pmatrix}$$

$$\mathfrak{R}_{B_{1g}} = \begin{pmatrix} c & 0 & 0 \\ 0 & -c & 0 \\ 0 & 0 & 0 \end{pmatrix}$$

$$\mathfrak{R}_{B_{2g}} = \begin{pmatrix} 0 & d & 0 \\ d & 0 & 0 \\ 0 & 0 & 0 \end{pmatrix}$$

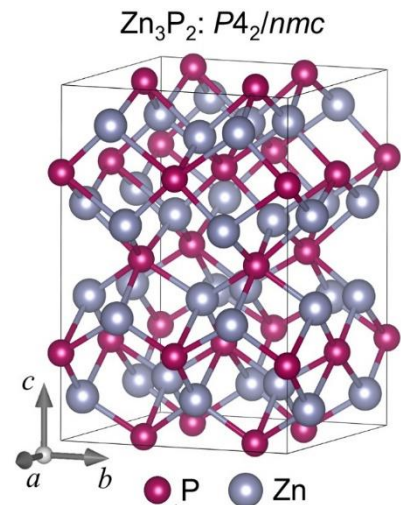
$$\mathfrak{R}_{E_g} = \begin{pmatrix} 0 & 0 & e \\ 0 & 0 & e \\ e & e & 0 \end{pmatrix}$$

Irreducible representations:

<https://www.cryst.ehu.es/#pointop>

Application: Identification of fundamental modes

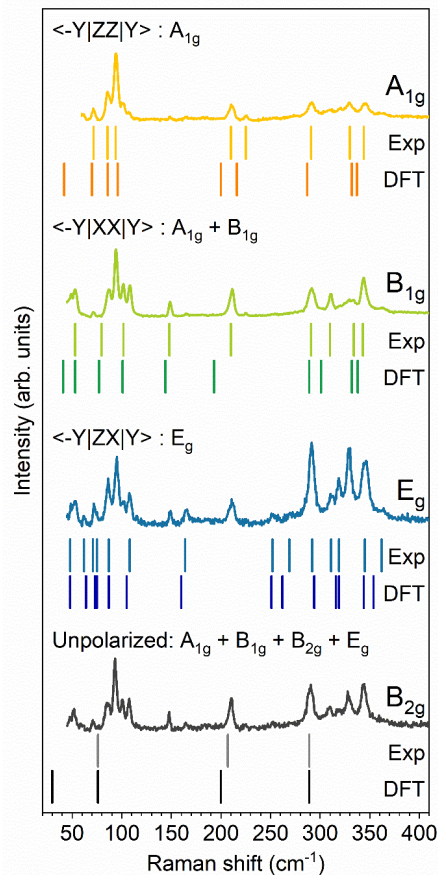
Symmetry of modes: polarization measurements



$$I \propto |v_i \mathcal{R}_{xyz} v_s|^2$$

$$v_i = (\cos \theta \quad 0 \quad \sin \theta)$$

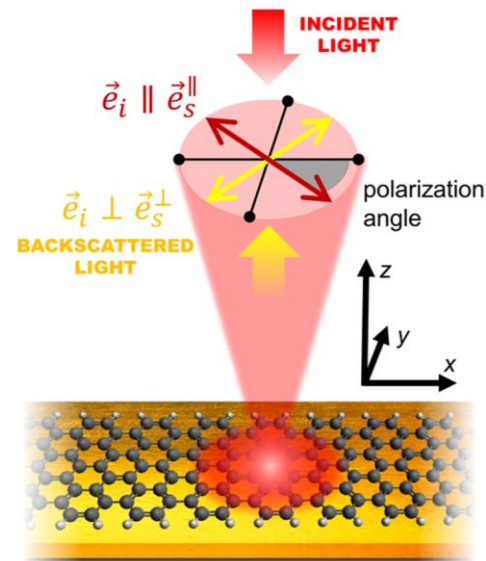
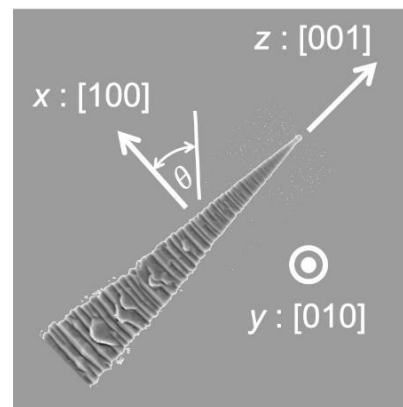
$$v_s^{\parallel} = \begin{pmatrix} \cos \theta \\ 0 \\ \sin \theta \end{pmatrix}; v_s^{\perp} = \begin{pmatrix} -\sin \theta \\ 0 \\ \cos \theta \end{pmatrix}$$



Proto notation

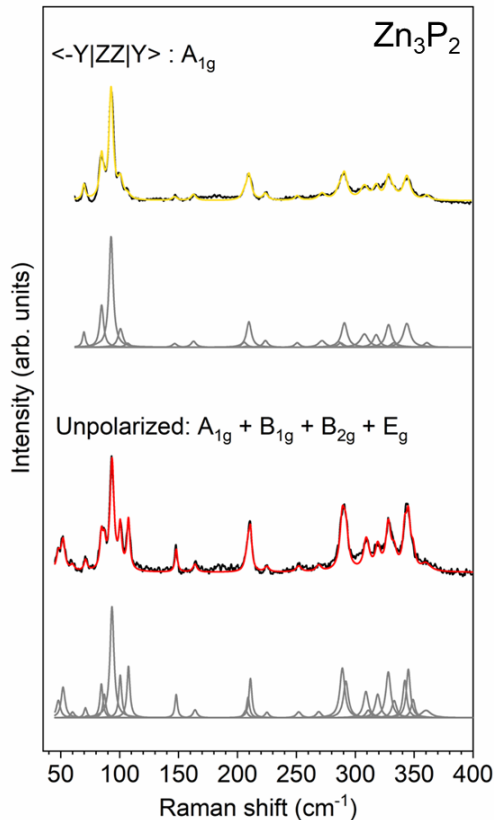
$$\langle -Y|ZX|Y \rangle$$

incoming radiation along **-y-axis** being polarized along **z-axis** with the backscattered (**y**) light polarized along **x-axis**



Application: Identification of fundamental modes

Identification of peak positions: deconvolution of Raman spectra



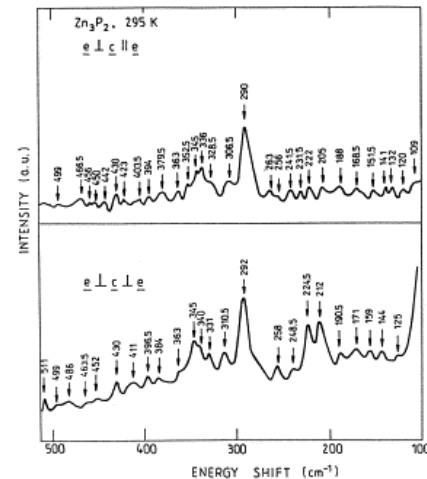
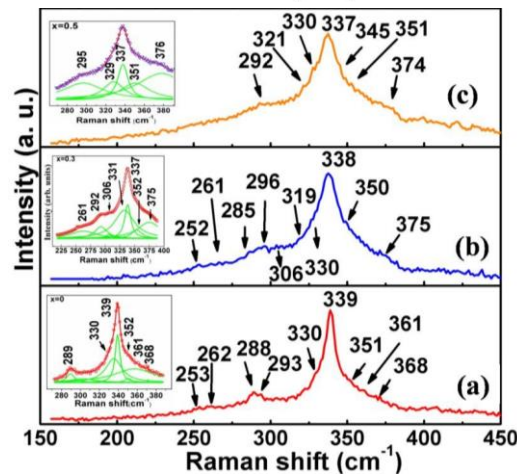
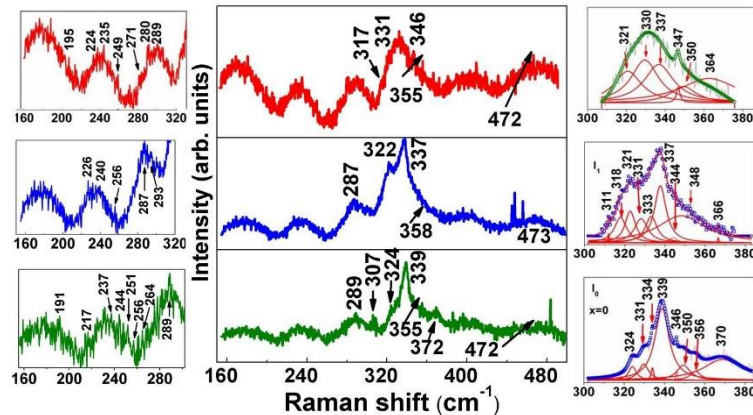
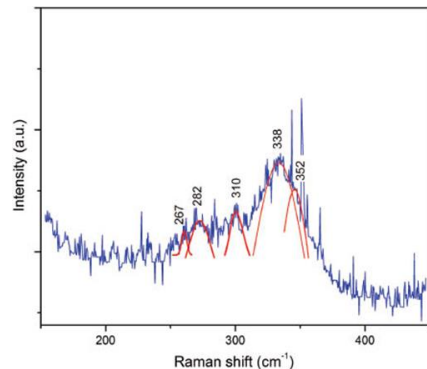
Procedure:

- 1) Determine which function is the most suitable for the investigated system (Lorentzian, Gaussian, Voigt)
- 2) Baseline correction
- 3) Minimum number of meaningful peaks
- 4) Widths should have similar values for all peaks (fundamental one-phonon modes)
- 5) Peak positions should not change for different measurement configurations
- 6) Peak intensity should be a free parameter

You need to know your system well!

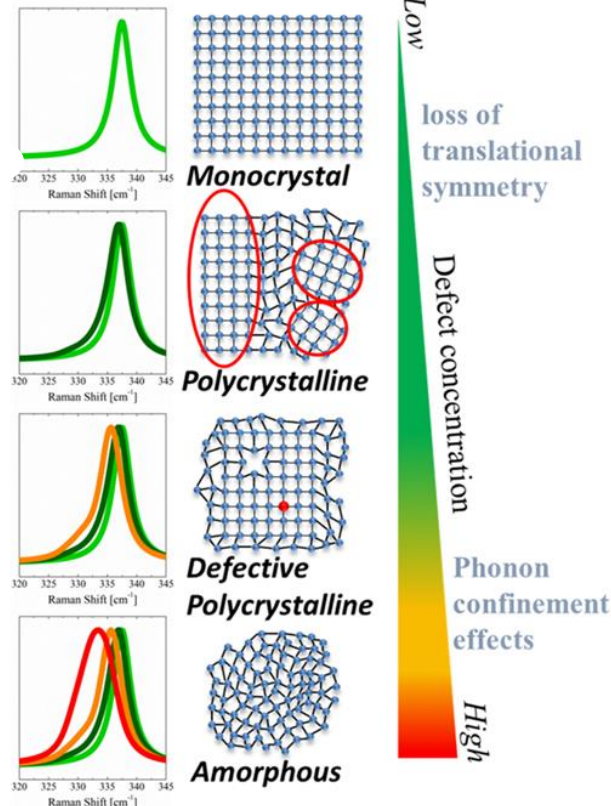
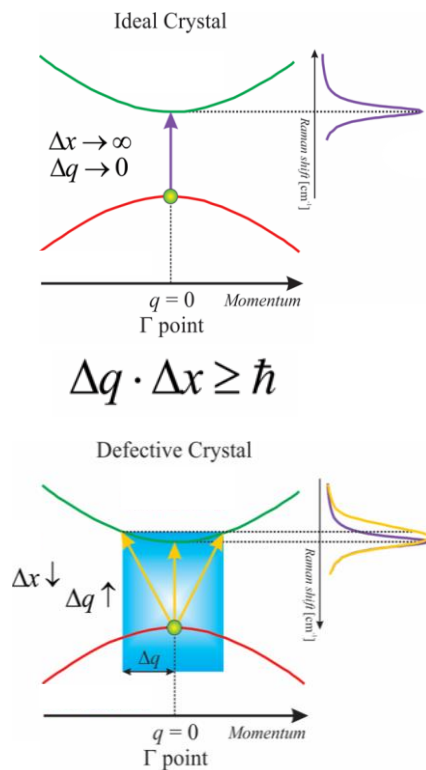
Application: Identification of fundamental modes

Identification of peak positions: **bad examples**

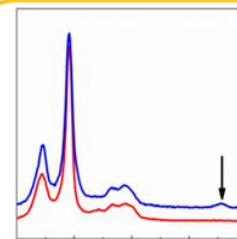


Raman spectroscopy: defect identification

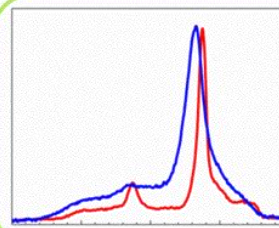
Raman features and defects



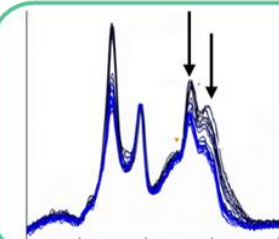
Effects of certain types of defects



Local vibrational modes leading to **additional bands** in the Raman spectra (**impurities**)

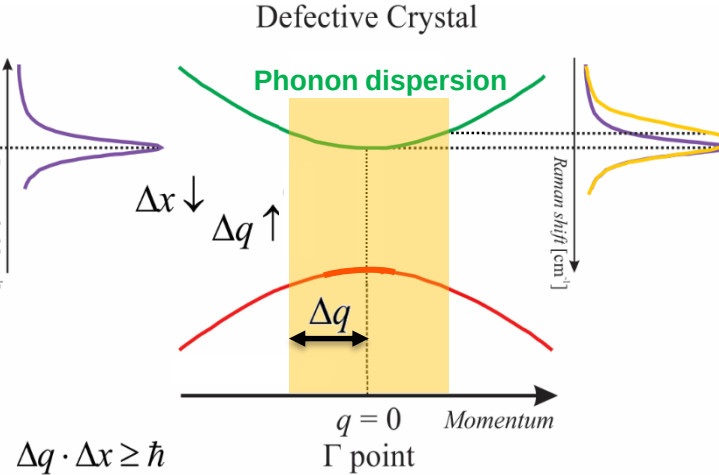
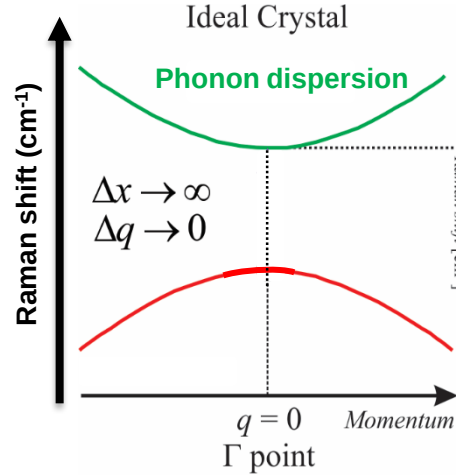
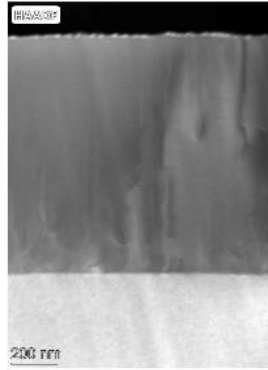


Symmetric broadening of modes: phonon life time (**defects**).

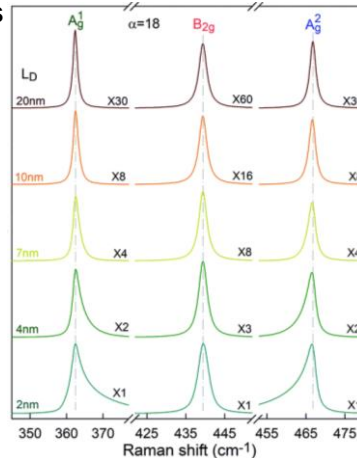
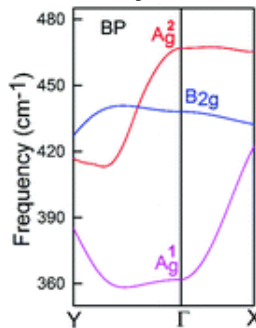


Change in the intensity of modes due to breaking in certain molecular bonds (**defects**).

Application: Defects – Phonon confinement model



Black phosphorus nanocrystals



$$I(\omega) = \int_0^{\Gamma N} \frac{9 j_1^2 (Lq/2) / (Lq/2)^2}{\left[\omega - (\omega(q) + \Delta\omega_c + \Delta\omega_s) \right]^2 + \frac{\Gamma^2}{4}} 4\pi q^2 dq$$

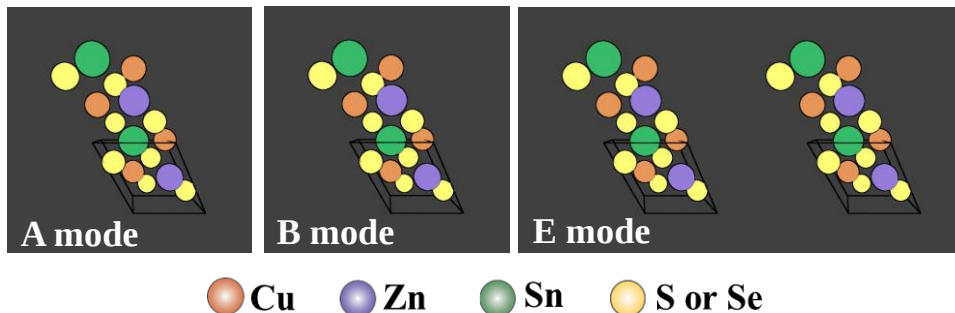
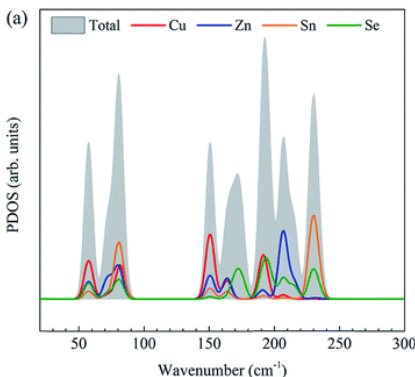
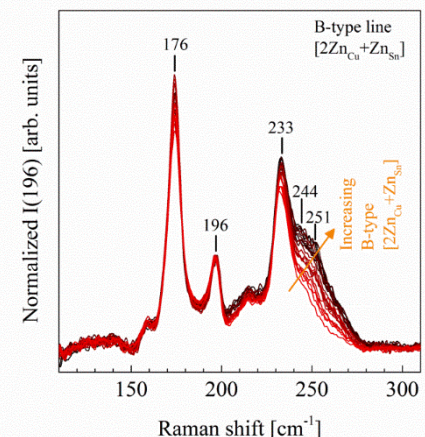
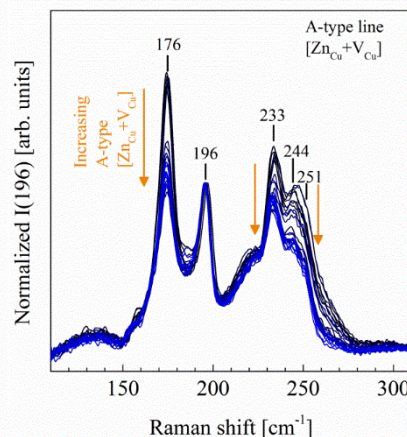
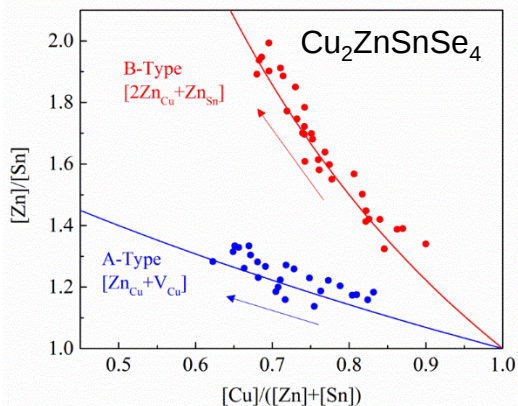
Correlation length (L)
Crystal quality estimation model

M. Dimitrievska et al., Acta Materialia 70, 272–280 (2014)

T. Lin Nanoscale, 10, 8704–8711 (2018)

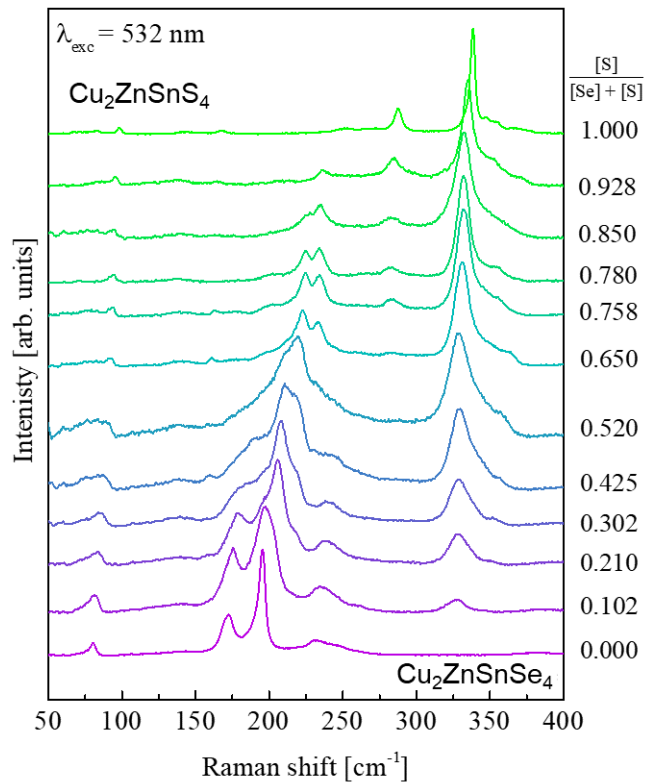
Application: Defect cluster identification

Combinatorial studies and DFT calculations:
 simple methodology for identifying defects in $\text{Cu}_2\text{ZnSnSe}_4$.



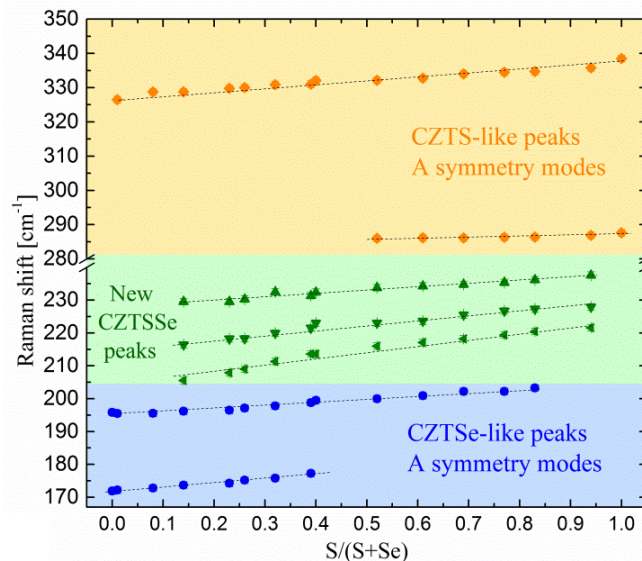
Application: Compositional assessment

The shape of Raman spectra is very sensitive to changes in composition.



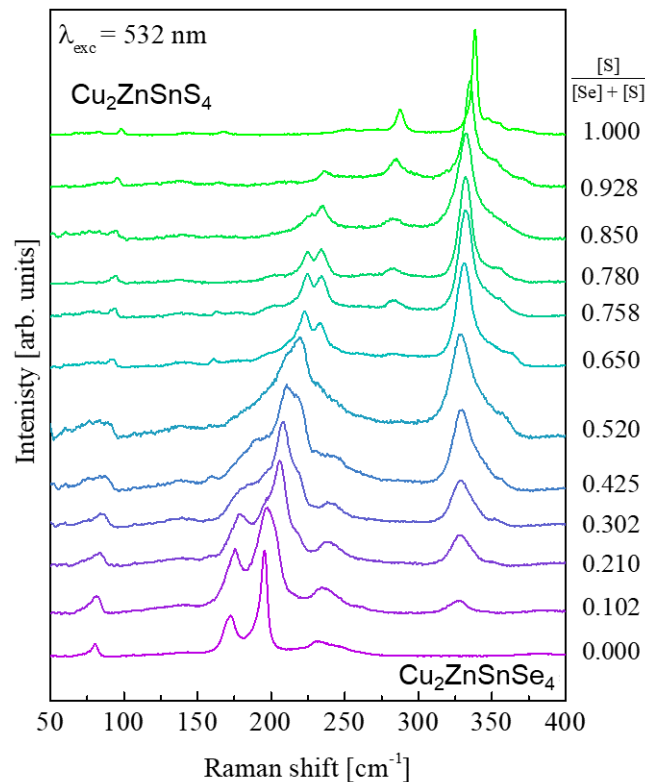
Building methodologies for compositional assessment:

- 1) Based on peak positions
- 2) Based on intensity ratio between certain modes



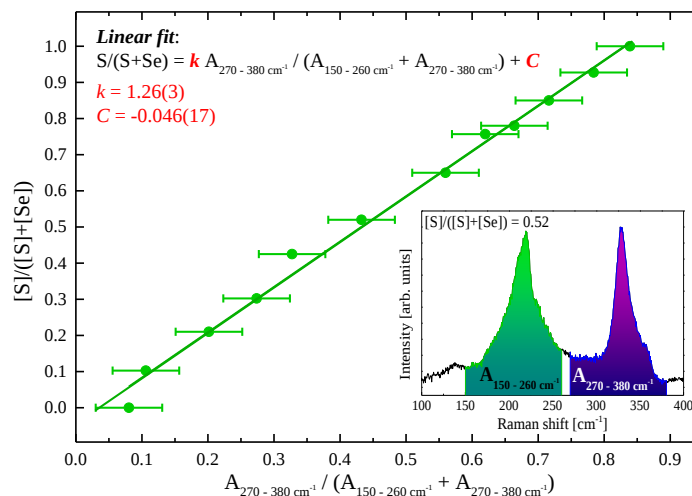
Application: Compositional assessment

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Building methodologies for compositional assessment:

- 1) Based on peak positions
- 2) Based on intensity ratio between certain modes

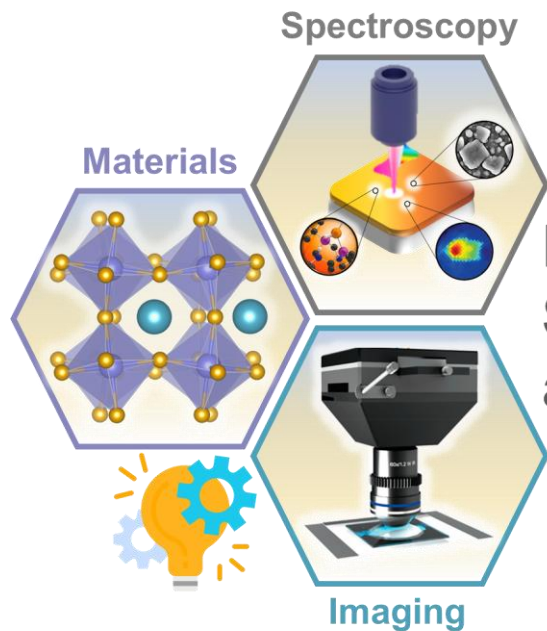


Conclusions

- **Introduction: Raman spectroscopy**
- **Considerations to take into account when performing the measurements:**
 - ☐ **Excitation energy**
 - ☐ **Power density and signal/noise ratio**
 - ☐ **System alignment and calibration**
- **What can you do with Raman spectroscopy?**
 - ☐ **Fundamental identification of modes**
 - ☐ **Crystal quality / defect assessment**
 - ☐ **Compositional assessment**

- **Theory: M. Cardona: Fundamentals of Semiconductors**
(<https://doi.org/10.1007/978-3-642-00710-1>)
- **Experiment: B. Schrader: Infrared and Raman Spectroscopy: Methods and Applications** (<https://doi.org/10.1002/9783527615438>)
- **Crystal and symmetry groups, irreducible representations, Raman active modes: Bilbao Crystallographic Server** (<https://www.cryst.ehu.es/>)

Thank you for your attention!



Nanomaterials Spectroscopy and Imaging



Dr. Elena
Mavrona



Dr. Erwin
Hack



Dr. Peter
Zolliker



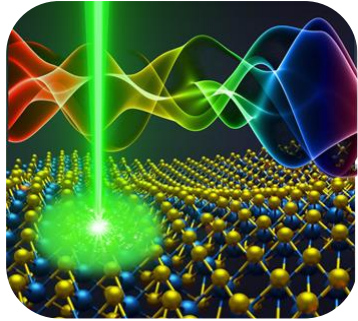
Angel
Labordet Álvarez



Alex
Weitnauer



**Nanomaterials
Spectroscopy
and Imaging**

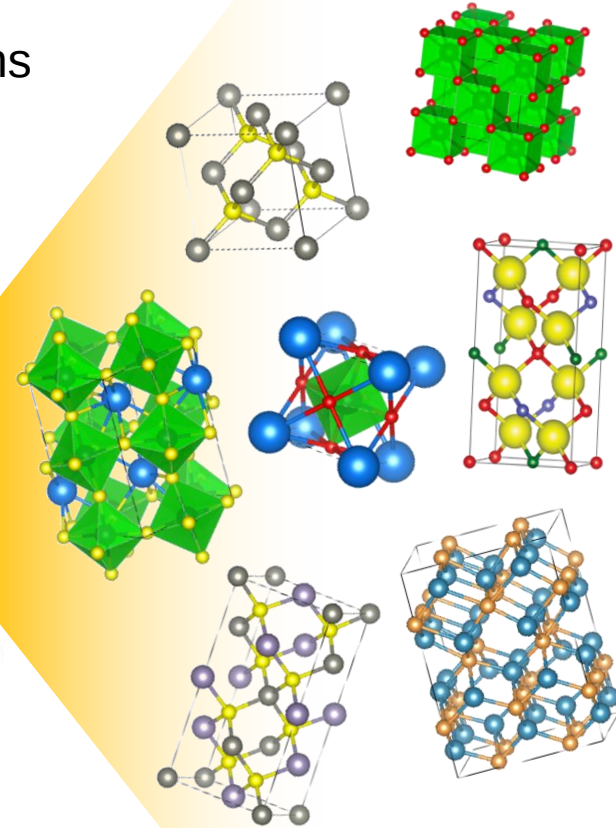
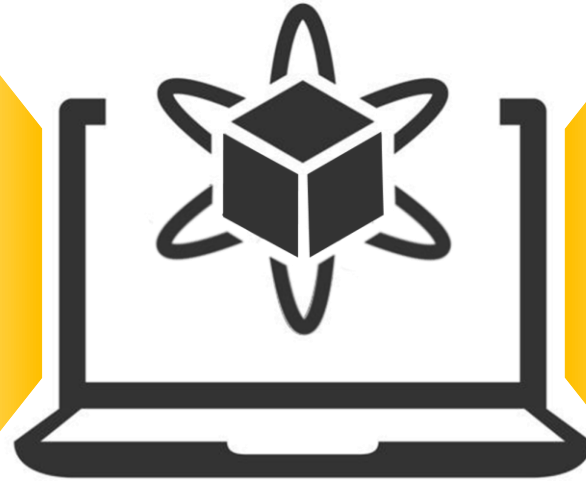
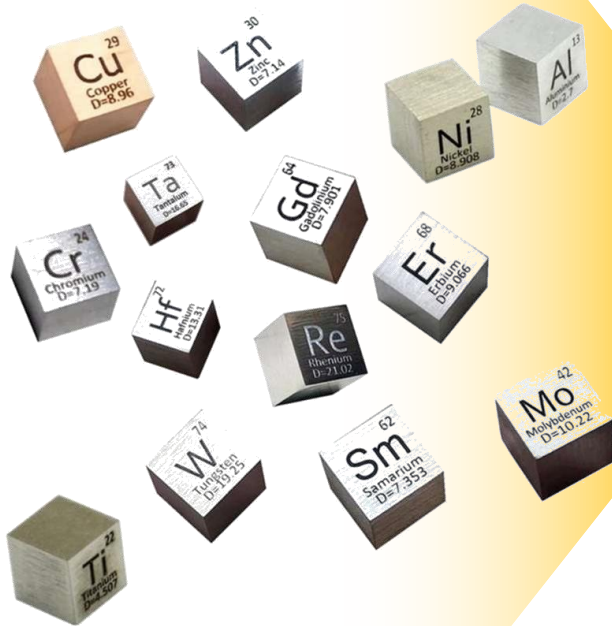


Raman spectroscopy at the nanoscale: from materials to devices

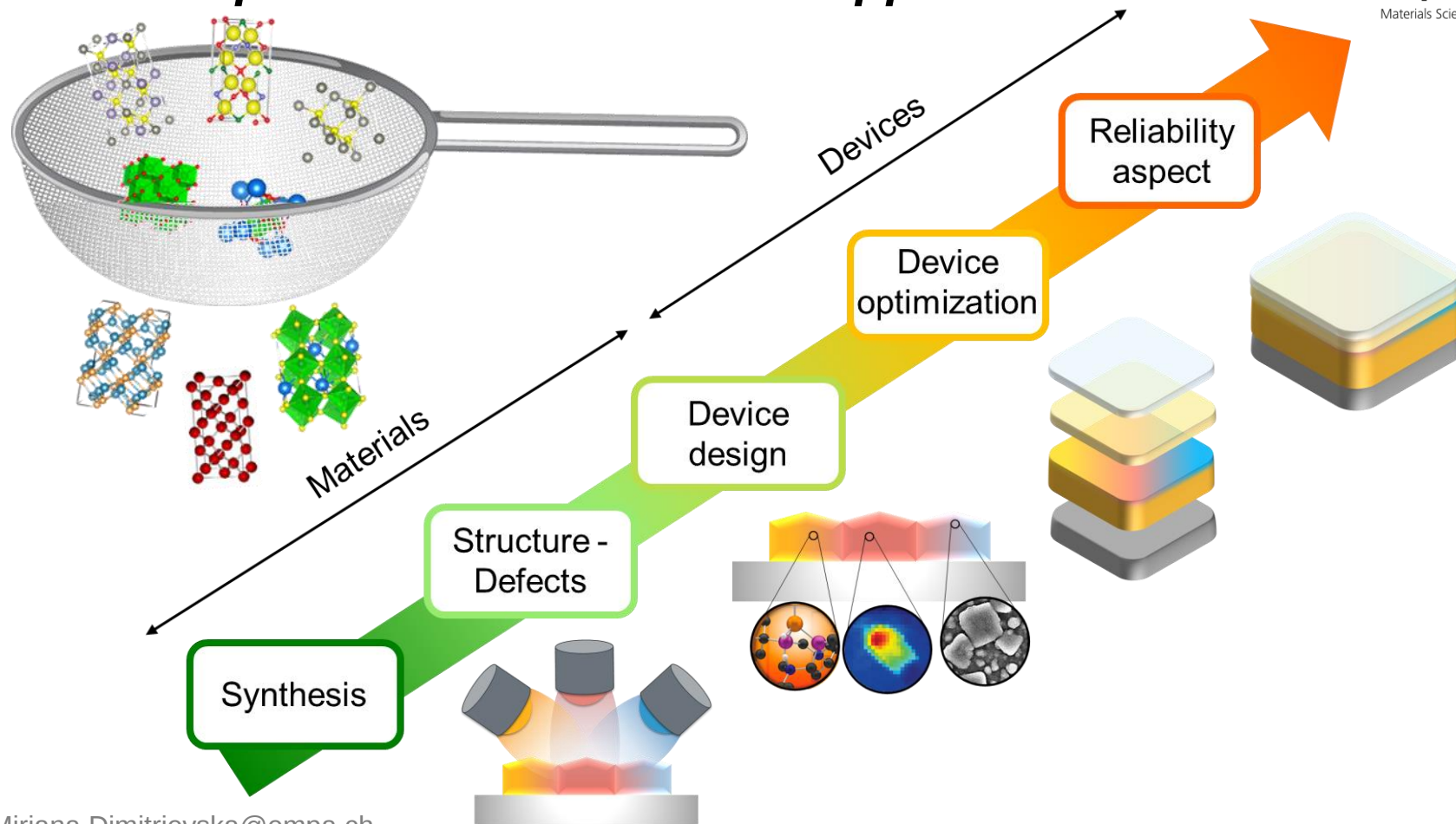
Mirjana Dimitrievska

Transport at Nanoscale Interfaces Laboratory
Swiss Federal Laboratories for Material Science and Technology (EMPA)
Switzerland

Advanced modeling/simulations
Machine learning

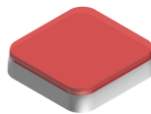


Selection process of materials for applications

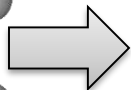
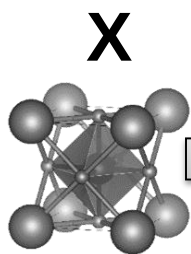


Materials design roadmap: Raman perspective

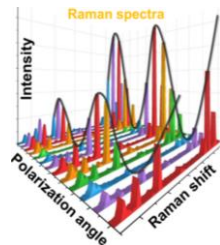
**Reference
Raman studies**



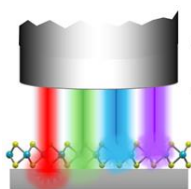
**Applied
Raman studies**



Theory:
Lattice
dynamics
calculations



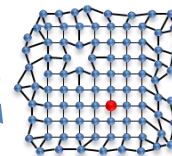
Experiment:
Polarization
Raman
measurements



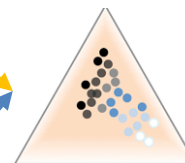
Experiment:
Multiwavelength
excitation Raman
measurements



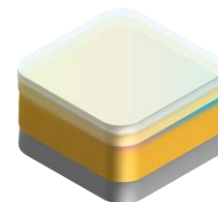
*high crystal quality,
stoichiometric samples*



**Defect
identification**



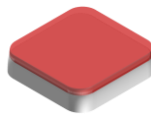
**Secondary phase
identification:**
phase diagram



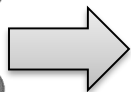
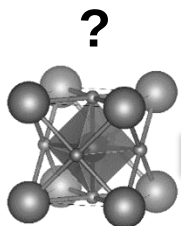
**Structure-function
correlation:**
Device performance

Materials design roadmap: Raman perspective

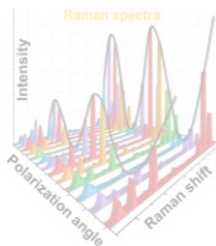
**Reference
Raman studies**



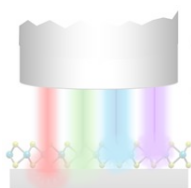
**Applied
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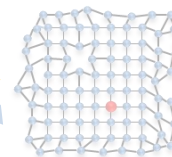
Experiment:
Polarization
Raman
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Experiment:
Multiwavelength
excitation Raman
measurements



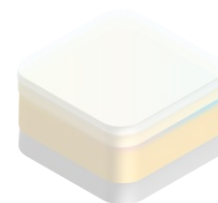
*high crystal quality,
stoichiometric samples*



**Defect
identification**



**Secondary phase
identification:**
phase diagram



**Structure-function
correlation:**
Device performance



Lattice Dynamics Calculations



Empa

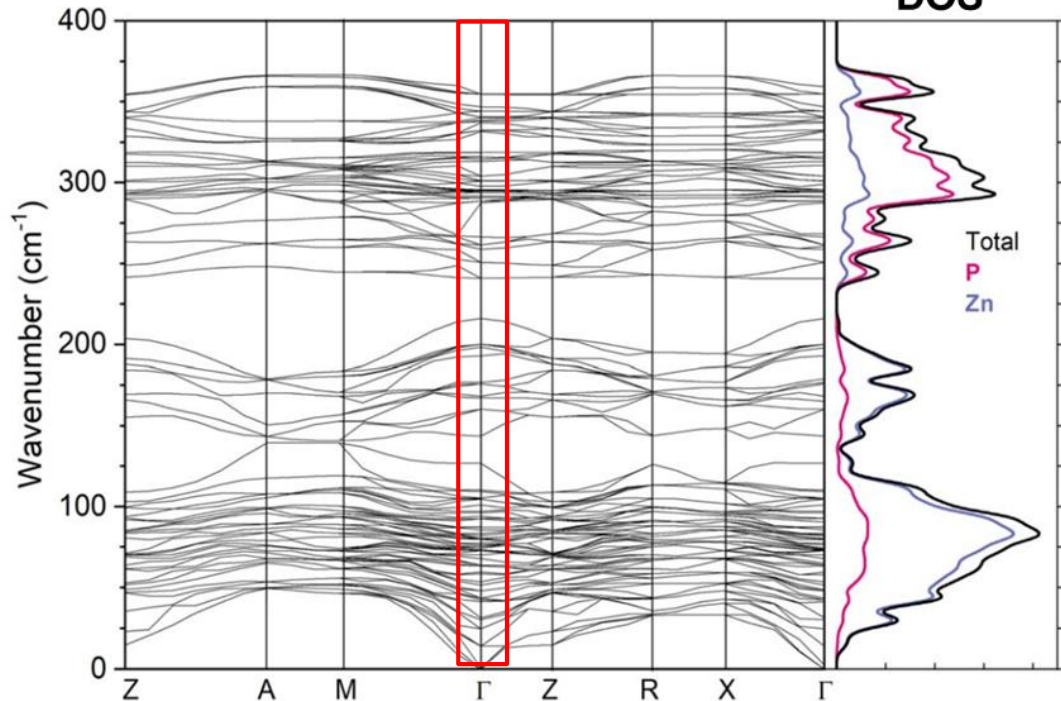
Materials Science and Technology

51

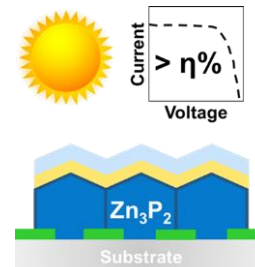
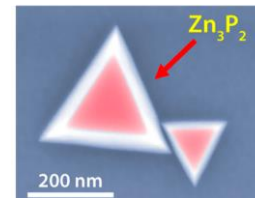
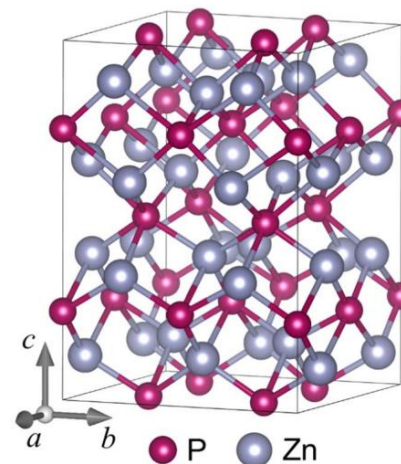
Zn_3P_2

Phonon dispersions

Phonon
DOS



Zn_3P_2 : $P4_2/nmc$



Irreducible representation:

$$\Gamma_{\text{total}} = 9A_{1g} + 5A_{2g} + 10B_{1g} + 4B_{2g} + 16E_g + 4A_{1u} + 10A_{2u} + 5B_{1u} + 9B_{2u} + 16E_u,$$

$$\Gamma_{\text{Raman}} = 9A_{1g} + 10B_{1g} + 4B_{2g} + 16E_g,$$

$$\Gamma_{\text{IR}} = 9A_{2u} + 15E_u,$$

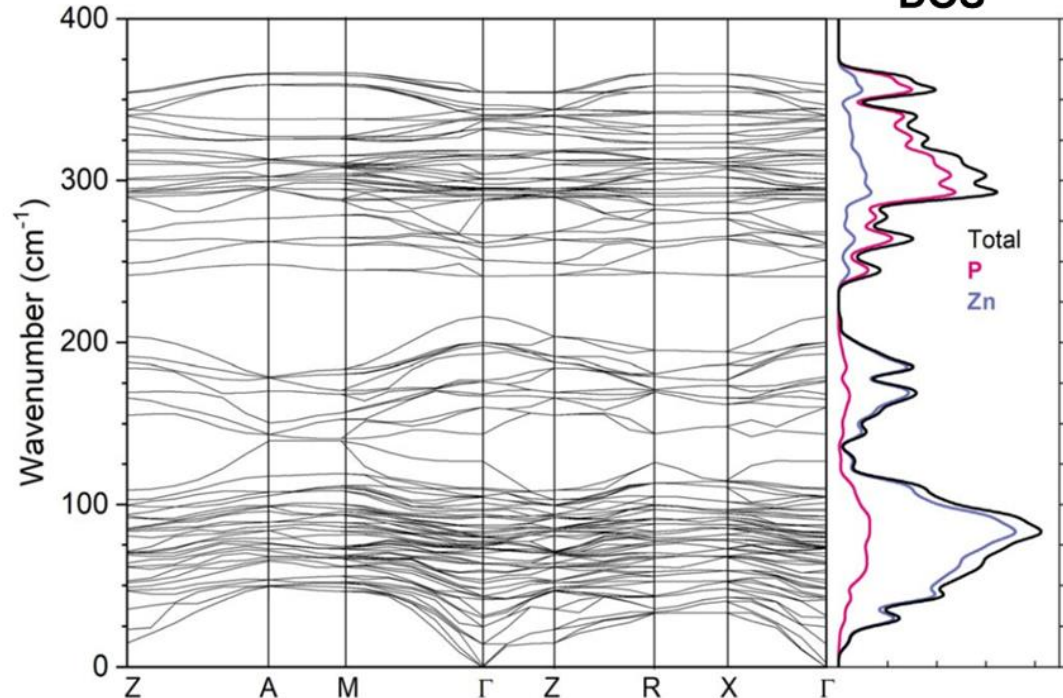
E.S. Stutz...M. Dimitrievska, Nanotechnology 32 085704 (2021)

M. Flor...M. Dimitrievska, Phys. Chem. Chem. Phys. 24 63 (2022)

Mirjana.Dimitrievska@empa.ch

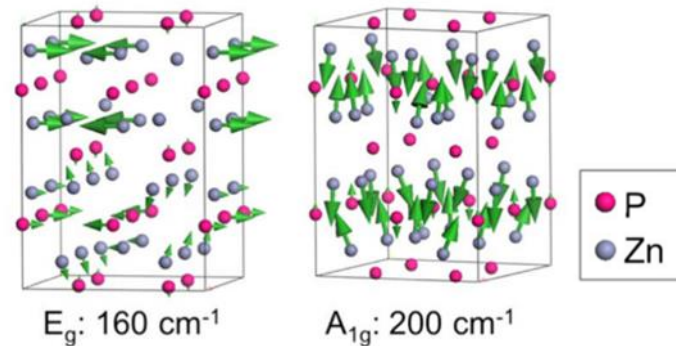


Phonon dispersions

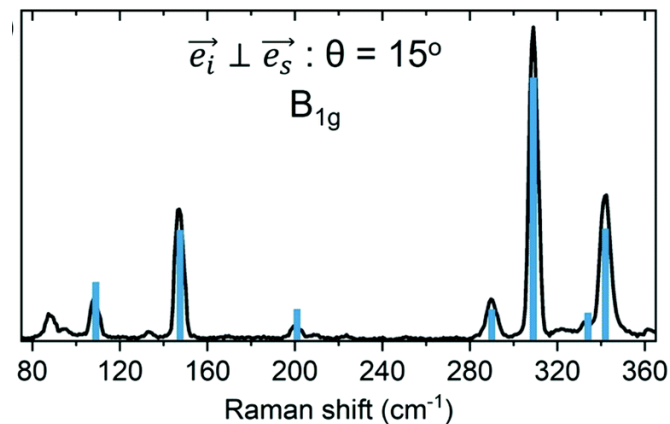


Phonon DOS

Vibrational patterns



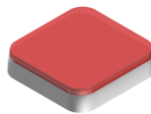
Simulated Raman spectra



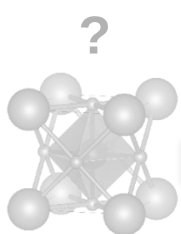
E.S. Stutz...M. Dimitrievska, Nanotechnology 32 085704 (2021)
M. Flor...M. Dimitrievska, Phys. Chem. Chem. Phys. 24 63 (2022)

Materials design roadmap: Raman perspective

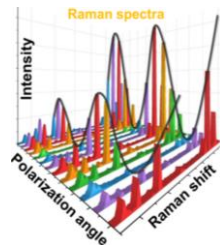
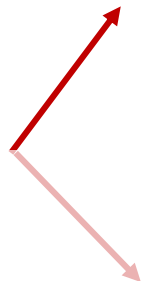
**Reference
Raman studies**



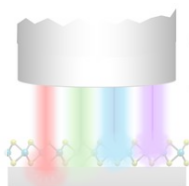
**Applied
Raman studies**



Theory:
Lattice
dynamics
calculations



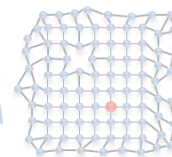
Experiment:
Polarization
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Experiment:
Multiwavelength
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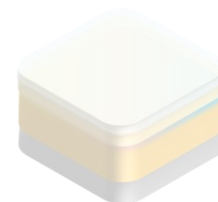
*high crystal quality,
stoichiometric samples*



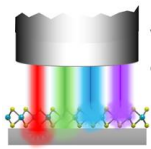
**Defect
identification**



**Secondary phase
identification:**
phase diagram

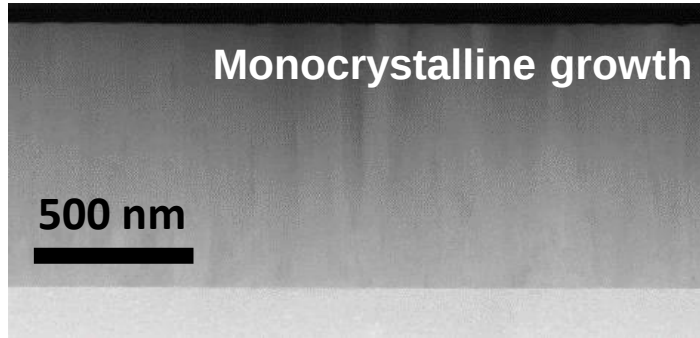


**Structure-function
correlation:**
Device performance

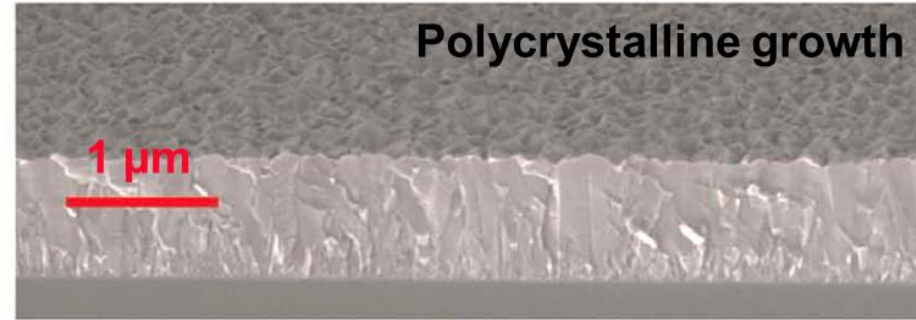


Experiment: synthesis of new materials

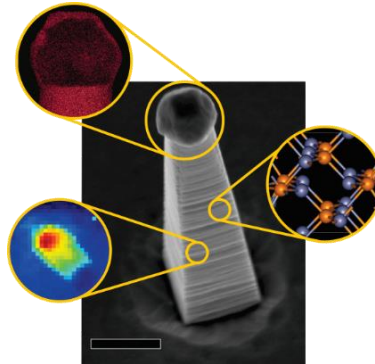
Desired



Usually obtained

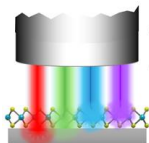


**Solution:
Nanowires**



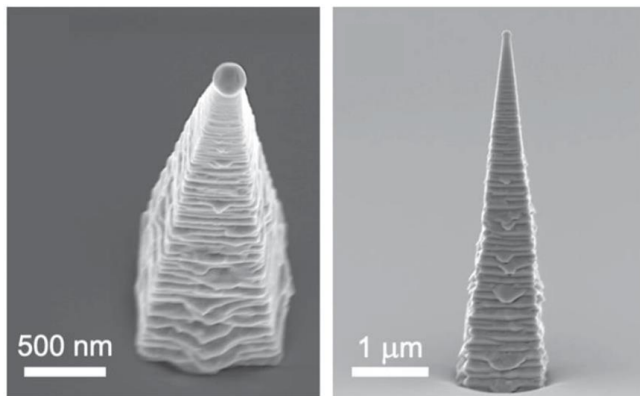
Advantage:
Single crystal growth

Disadvantage:
Characterization



Experiment: Reference Raman spectra

Zn₃P₂ vertical nanowires



Raman tensor

$$\mathcal{R}_{A_{1g}} = \begin{pmatrix} a & 0 & 0 \\ 0 & a & 0 \\ 0 & 0 & b \end{pmatrix}$$

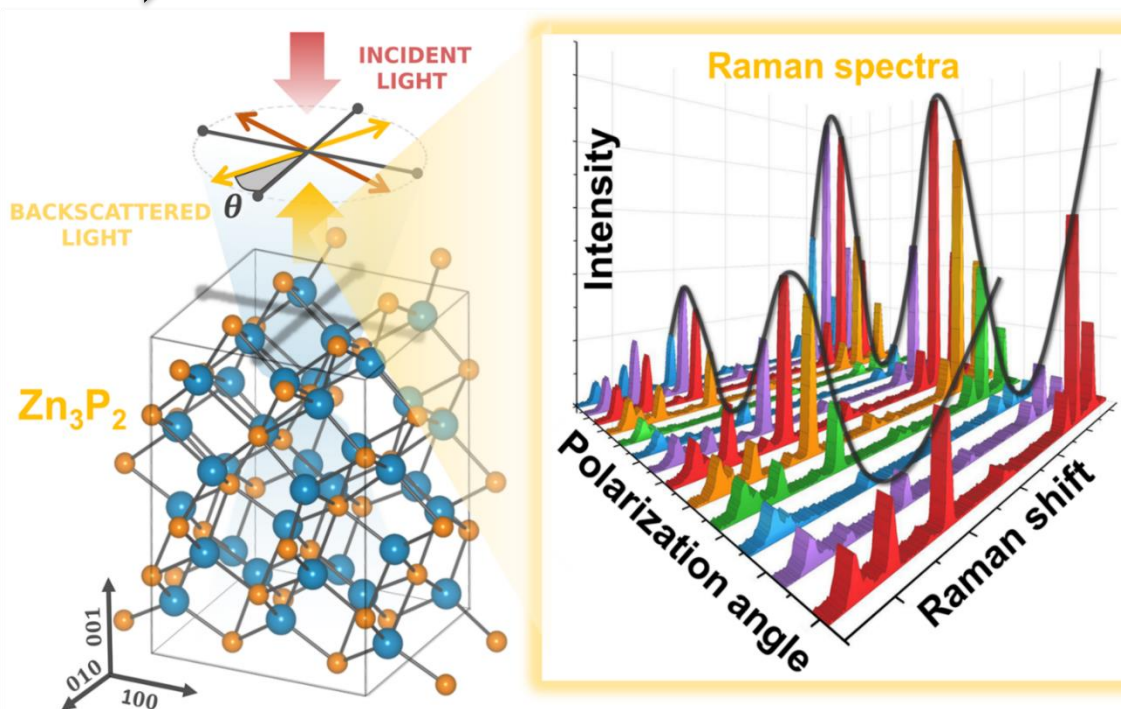
Raman intensity

$$I_S \propto C(\omega_p) \left| \vec{e}_i \cdot \mathcal{R} \cdot \vec{e}_s \right|^2$$

Mirjana.Dimitrievska@empa.ch

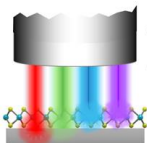


Polarization Raman spectroscopy

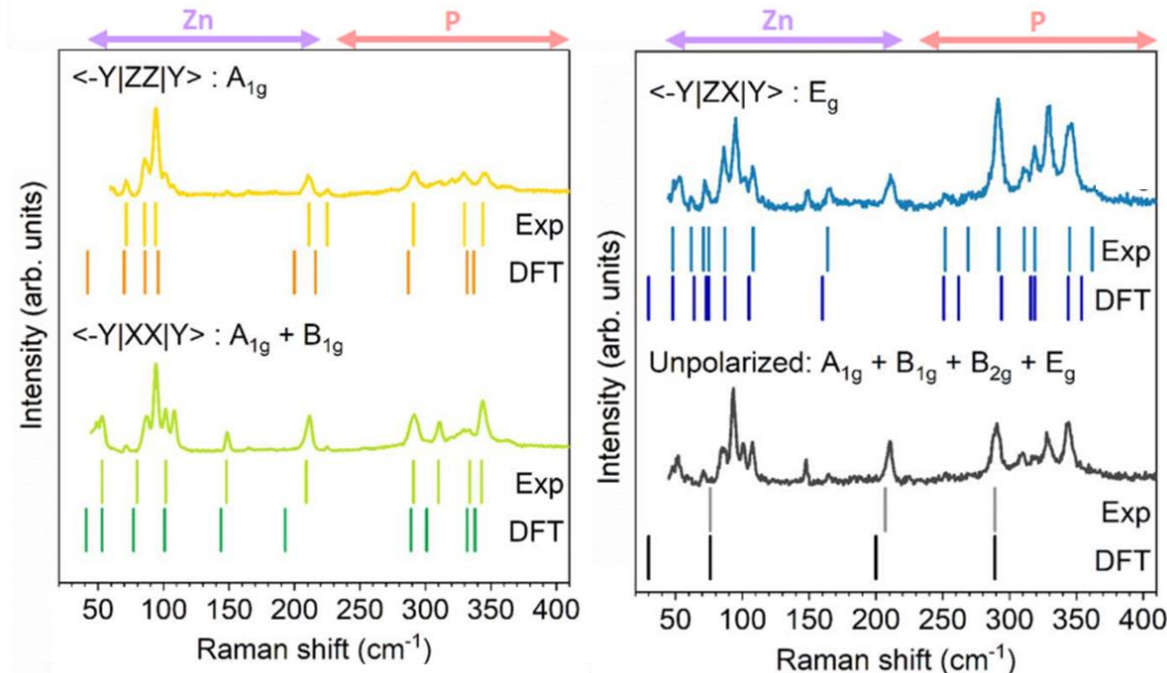
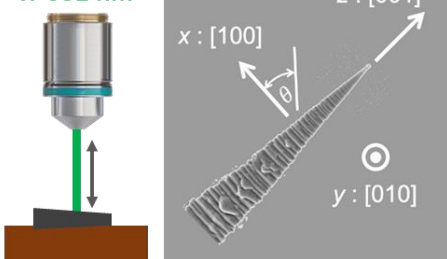


E.S. Stutz...M. Dimitrievska, Nanotechnology 32 085704 (2021)
 M. Flor...M. Dimitrievska, Phys. Chem. Chem. Phys. 24 63 (2022)

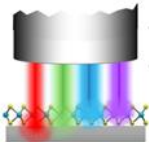
Experiment: Polarization Raman spectroscopy



Measurements geometry

 $\lambda = 532 \text{ nm}$


E.S. Stutz...M. Dimitrievska, Nanotechnology 32 085704 (2021)
 M. Flor...M. Dimitrievska, Phys. Chem. Chem. Phys. 24 63 (2022)



Identification of peak positions: deconvolution of Raman spectra

Minimum
number of
meaningful
peaks

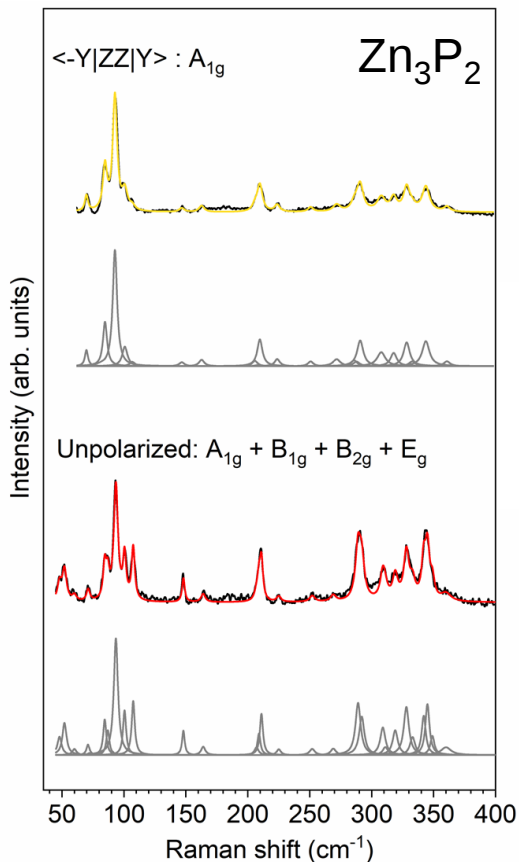
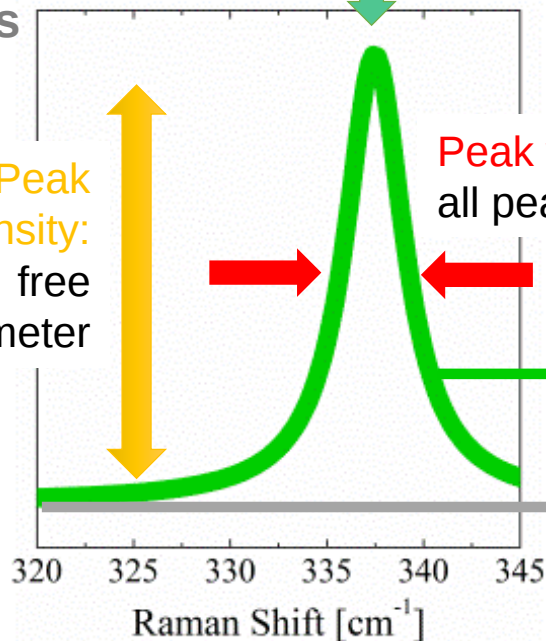
Peak positions: constant for different measurement configurations

Peak
intensity:
free
parameter

Peak widths: similar values for all peaks (one phonon modes)

Lorentzian,
Gaussian, Voigt

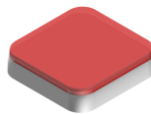
Baseline correction



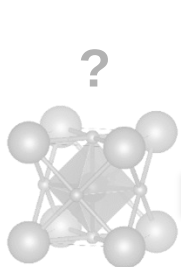
E.S. Stutz...M. Dimitrievska, Nanotechnology 32 085704 (2021)
M. Flor...M. Dimitrievska, Phys. Chem. Chem. Phys. 24 63 (2022)

Materials design roadmap: Raman perspective

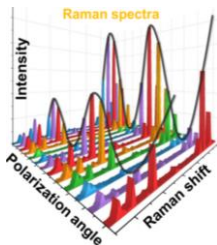
**Reference
Raman studies**



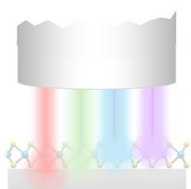
**Applied
Raman studies**



Theory:
Lattice
dynamics
calculations



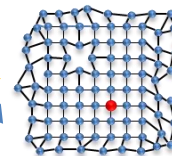
Experiment:
Polarization
Raman
measurements



Experiment:
Multiwavelength
excitation Raman
measurements



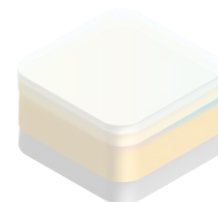
*high crystal quality,
stoichiometric samples*



**Defect
identification**



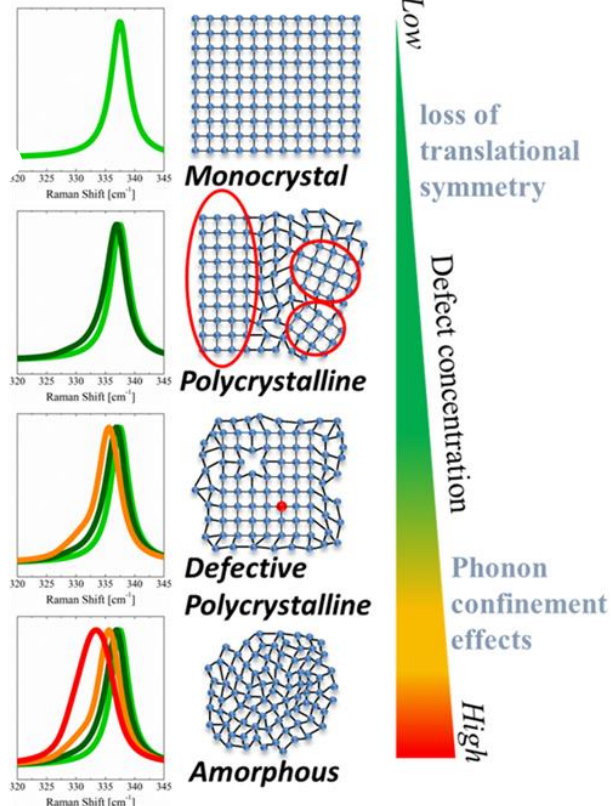
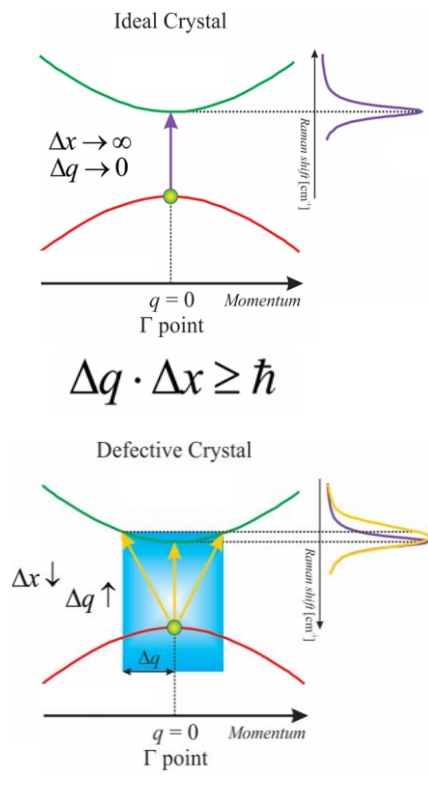
**Secondary phase
identification:**
phase diagram



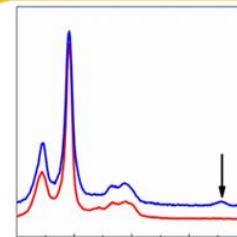
**Structure-function
correlation:**
Device performance

Raman spectroscopy: defect identification

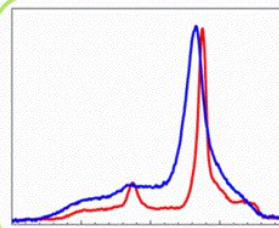
Raman features and defects



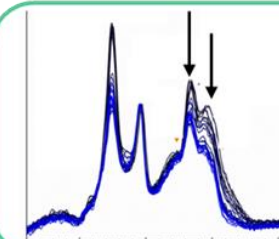
Effects of certain types of defects



Local vibrational modes leading to **additional bands** in the Raman spectra (**impurities**)



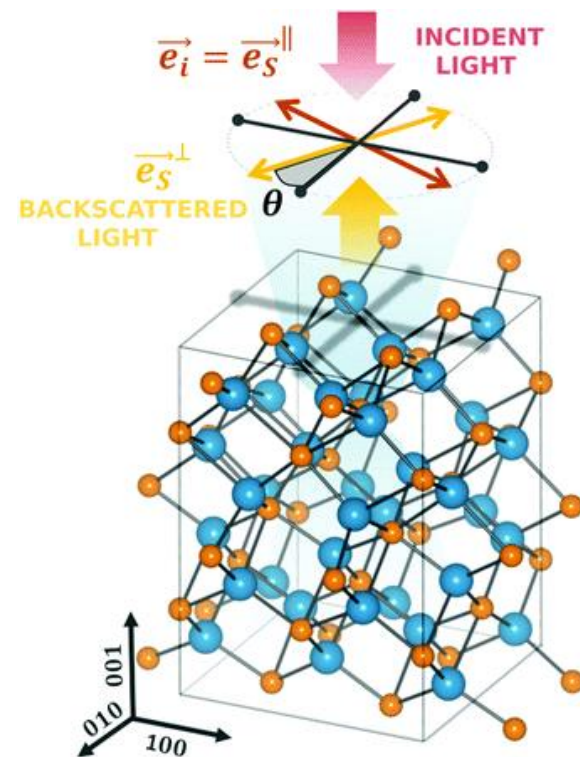
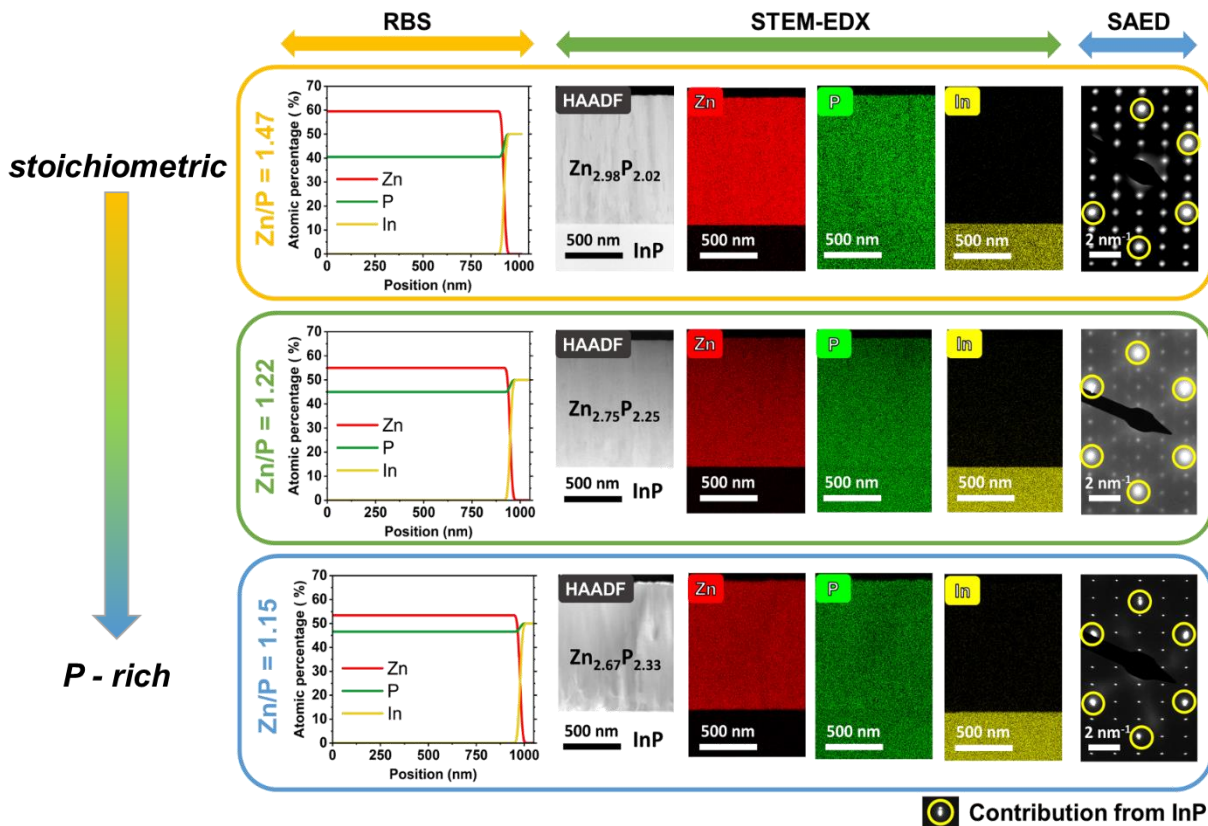
Symmetric broadening of modes: phonon life time (**defects**).

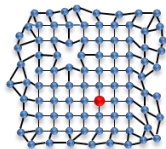


Change in the intensity of modes due to breaking in certain molecular bonds (**defects**).

Raman spectroscopy: defect identification

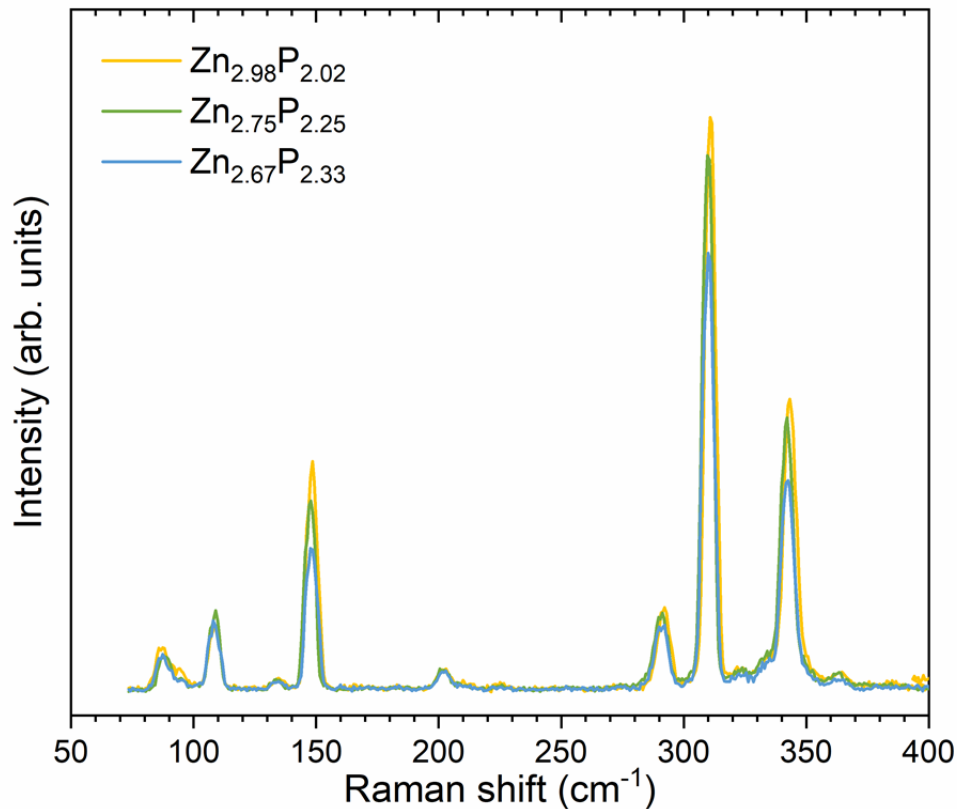
Off-stoichiometric $\text{Zn}_{3-x}\text{P}_{2+x}$ monocrystalline films



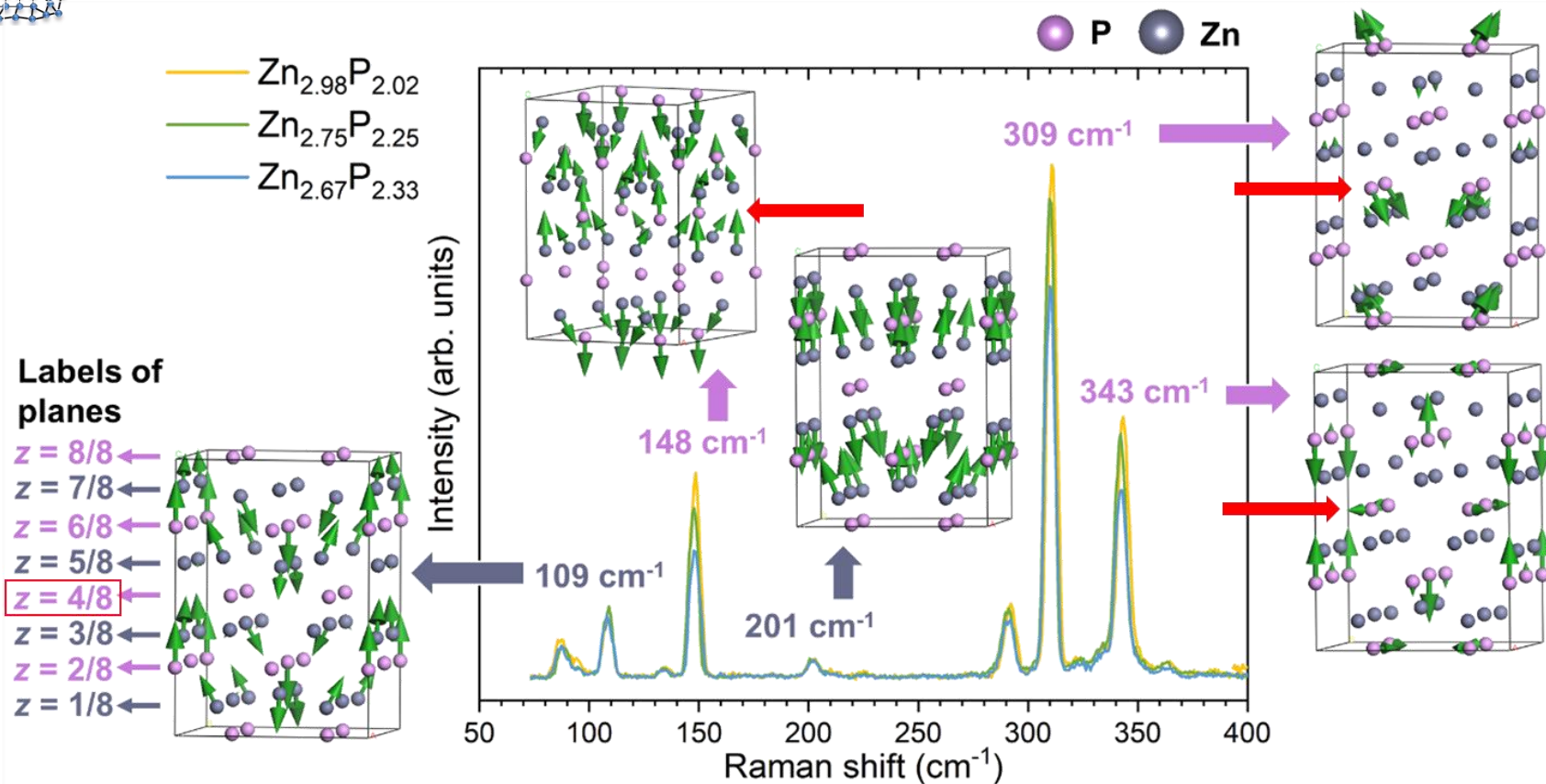


Raman spectroscopy: defect identification

Only B_{1g} Raman modes

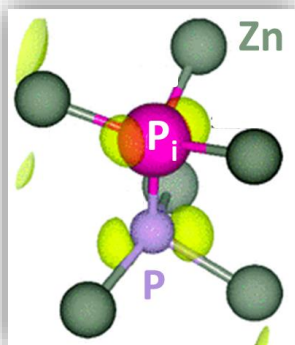


Raman spectroscopy: defect identification



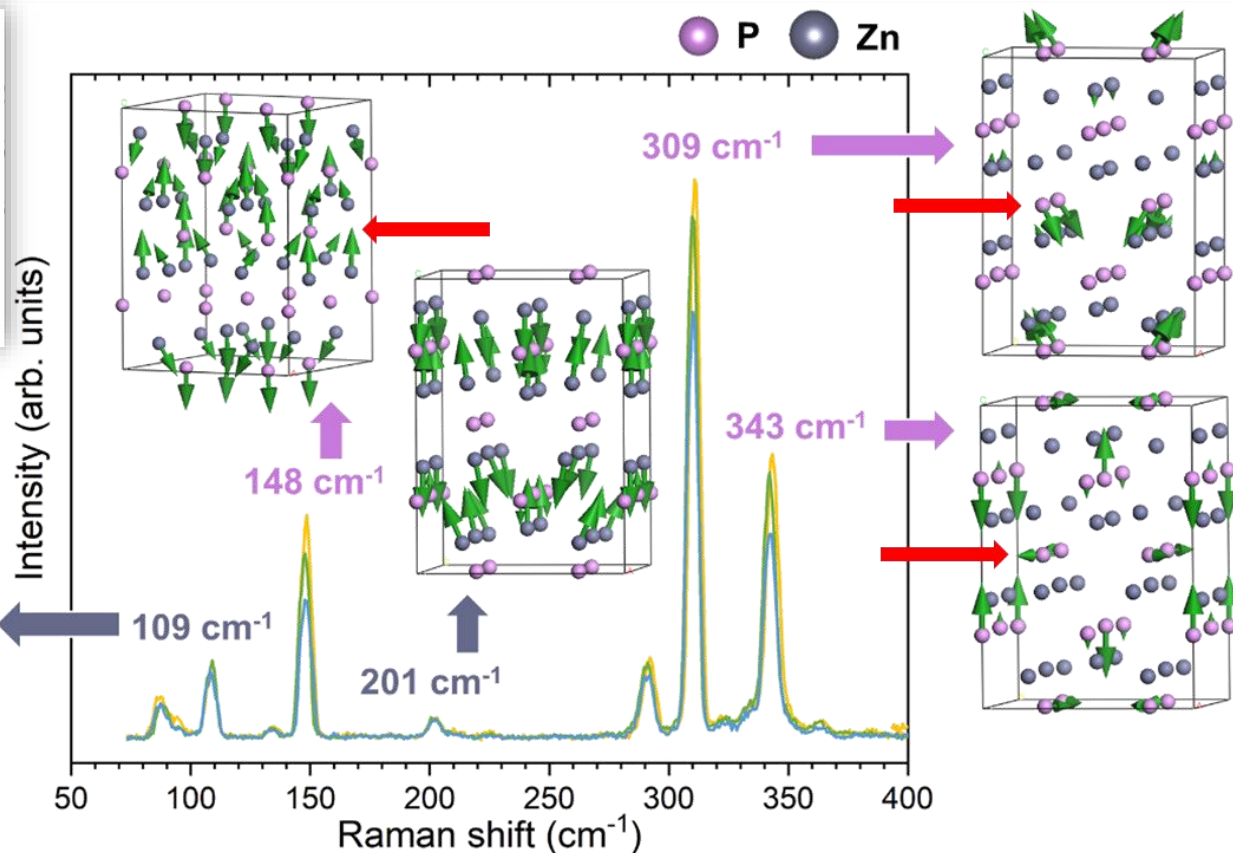
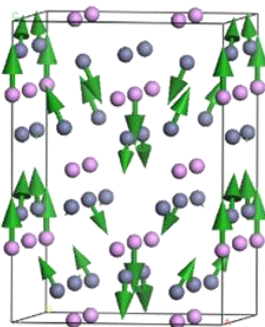
Raman spectroscopy: defect identification

P –
interstitials
 (DFT defect calculations)



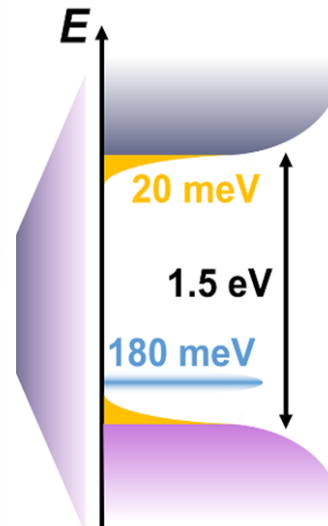
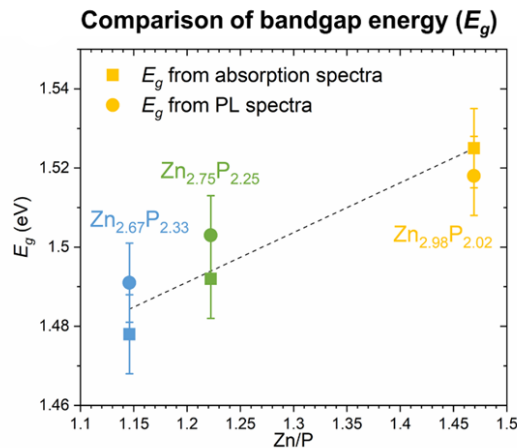
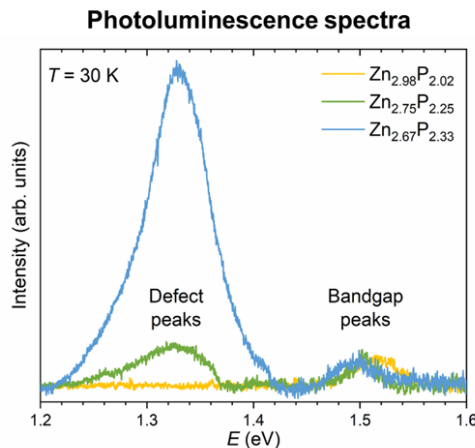
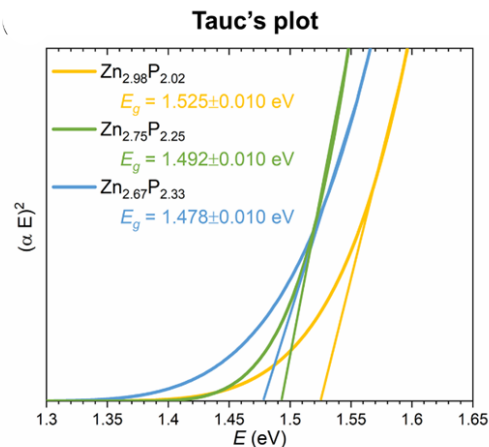
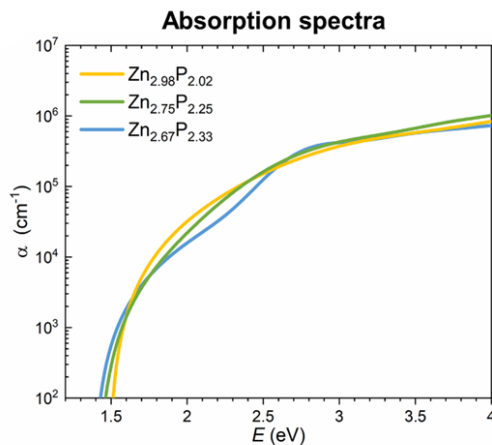
Labels of planes

$z = 8/8$ ←
 $z = 7/8$ ←
 $z = 6/8$ ←
 $z = 5/8$ ←
 $z = 4/8$ ←
 $z = 3/8$ ←
 $z = 2/8$ ←
 $z = 1/8$ ←



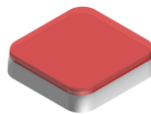
Raman spectroscopy: defect identification

*Tunable
optoelectronic
properties*

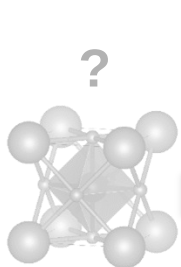


Materials design roadmap: Raman perspective

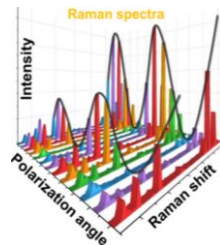
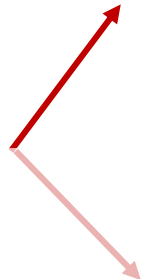
**Reference
Raman studies**



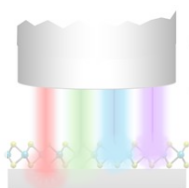
**Applied
Raman studies**



Theory:
Lattice
dynamics
calculations



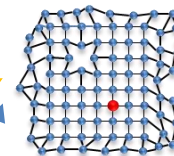
Experiment:
Polarization
Raman
measurements



Experiment:
Multiwavelength
excitation Raman
measurements



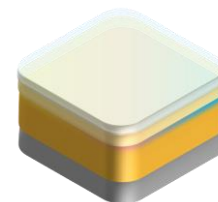
*high crystal quality,
stoichiometric samples*



**Defect
identification**



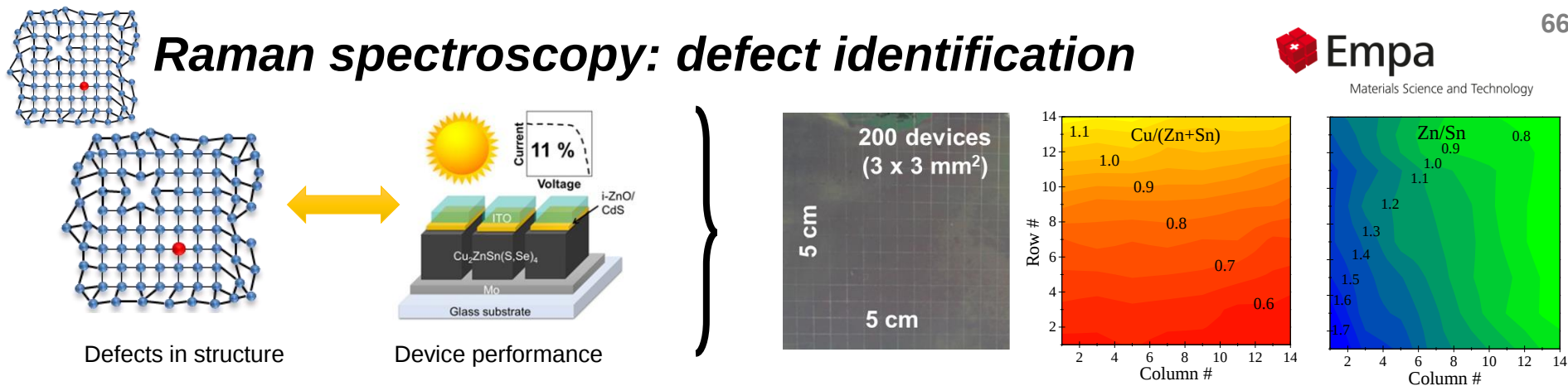
**Secondary phase
identification:**
phase diagram



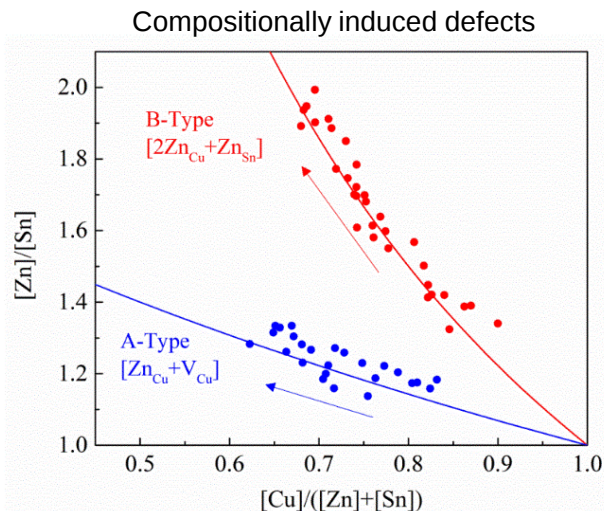
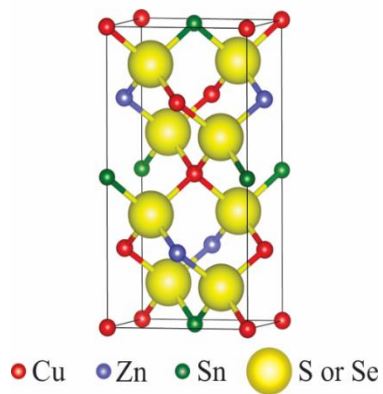
**Structure-function
correlation:**
Device performance



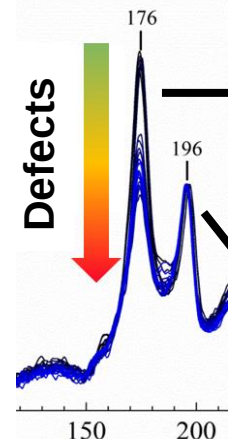
Raman spectroscopy: defect identification



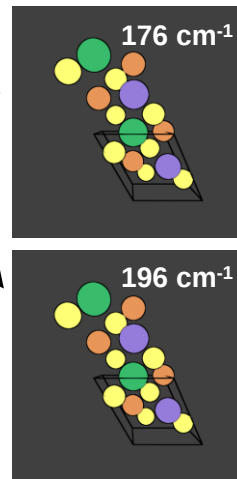
Kesterite: Cu₂ZnSnSe₄



Experiment



DFT calculations

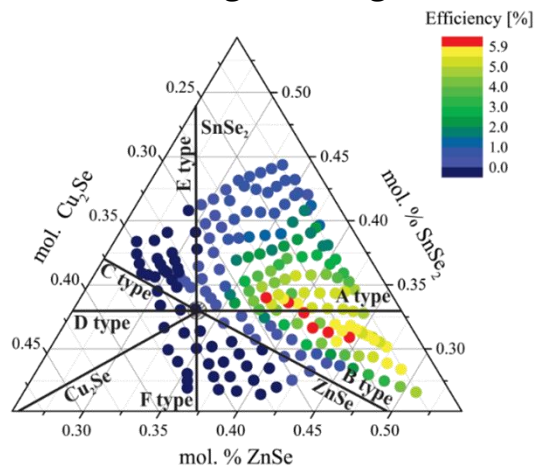


M. Dimitrievska et al. **J. Mater. Chem. A**, 7, 13293-13304 (2019)

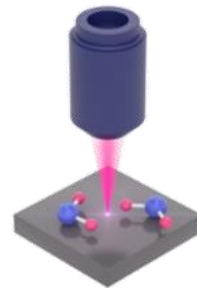
M. Dimitrievska et al. **Solar Energy Materials & Solar Cells** 157, 462 (2016)

Raman spectroscopy: defect identification

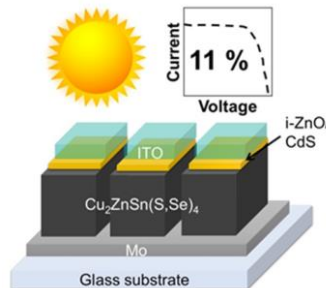
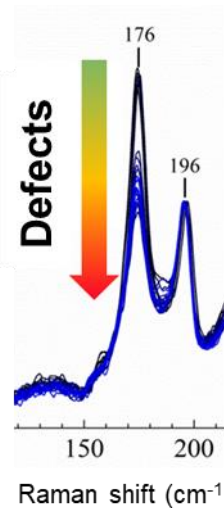
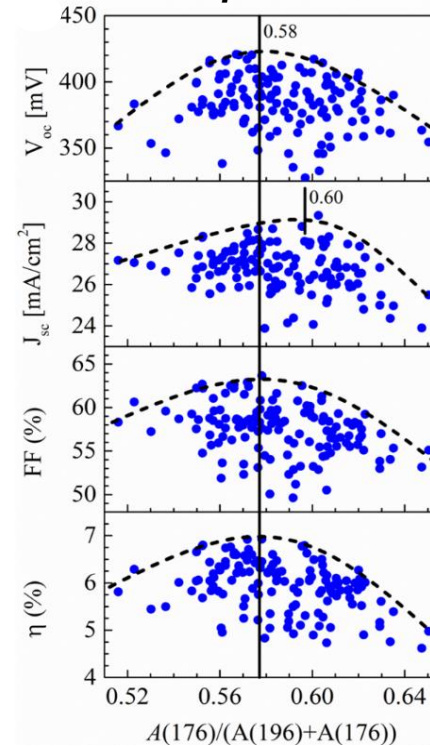
Defect engineering



Raman spectroscopy



Device performance

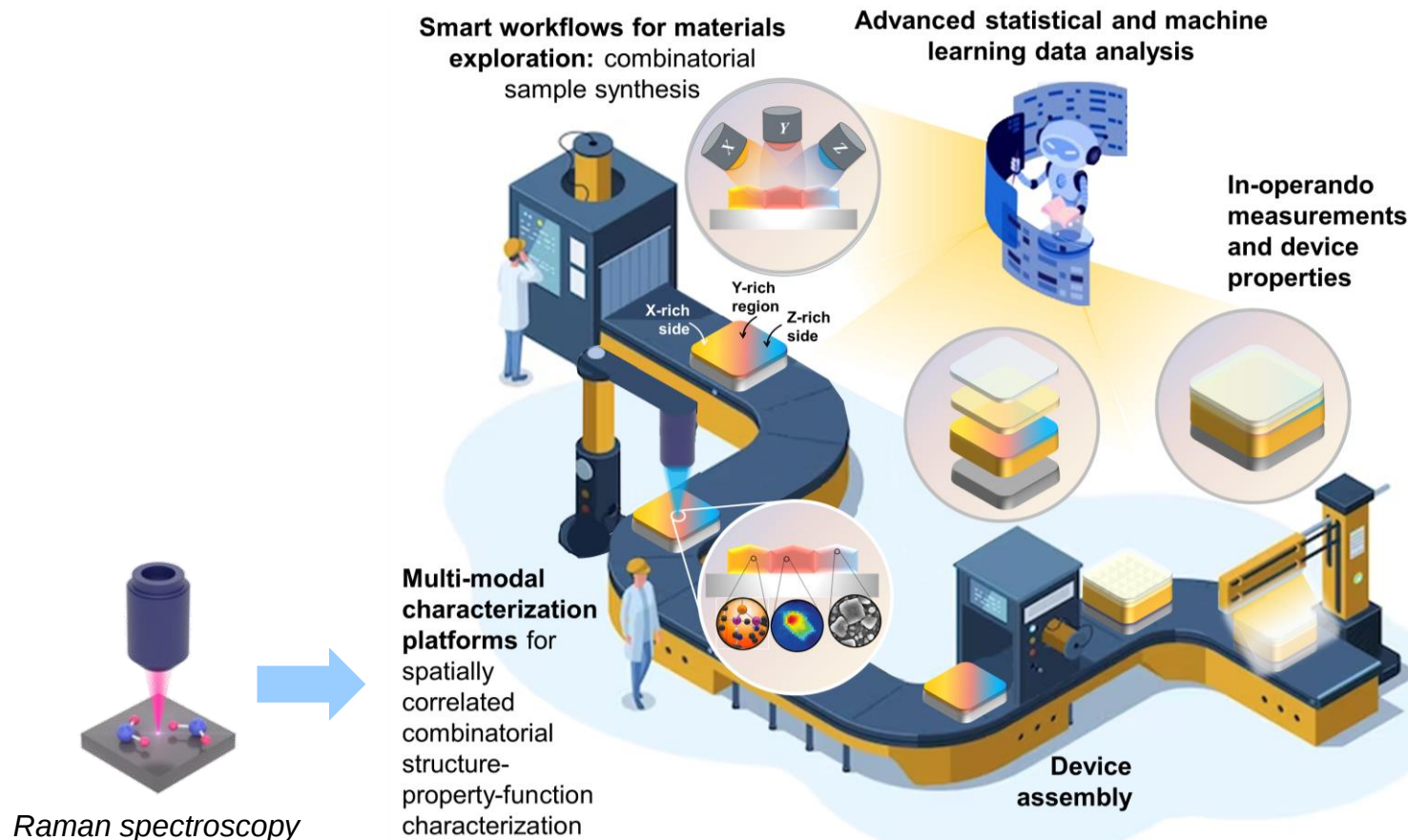


Defects

M. Dimitrievska et al. J. Mater. Chem. A, 7, 13293-13304 (2019)

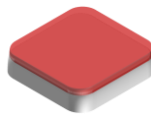
M. Dimitrievska et al. Solar Energy Materials & Solar Cells 157, 462 (2016)

Accelerated materials development

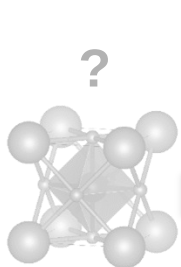


Materials design roadmap: Raman perspective

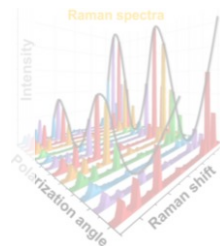
**Reference
Raman studies**



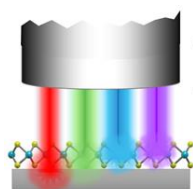
**Applied
Raman studies**



Theory:
Lattice
dynamics
calculations



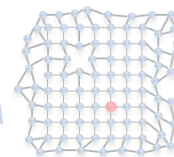
Experiment:
Polarization
Raman
measurements



Experiment:
Multiwavelength
excitation Raman
measurements



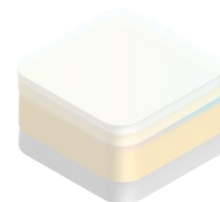
*high crystal quality,
stoichiometric samples*



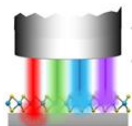
**Defect
identification**



**Secondary phase
identification:**
phase diagram



**Structure-function
correlation:**
Device performance



Multiwavelength excitation Raman spectroscopy



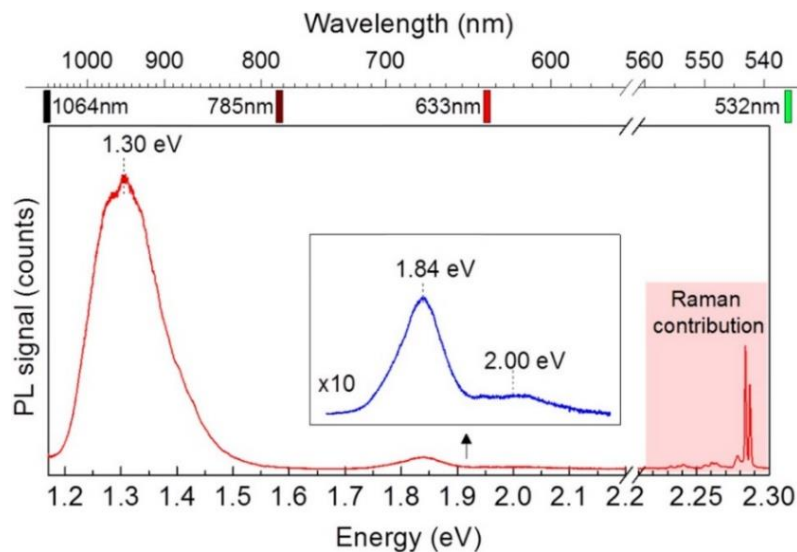
Empa

Materials Science and Technology

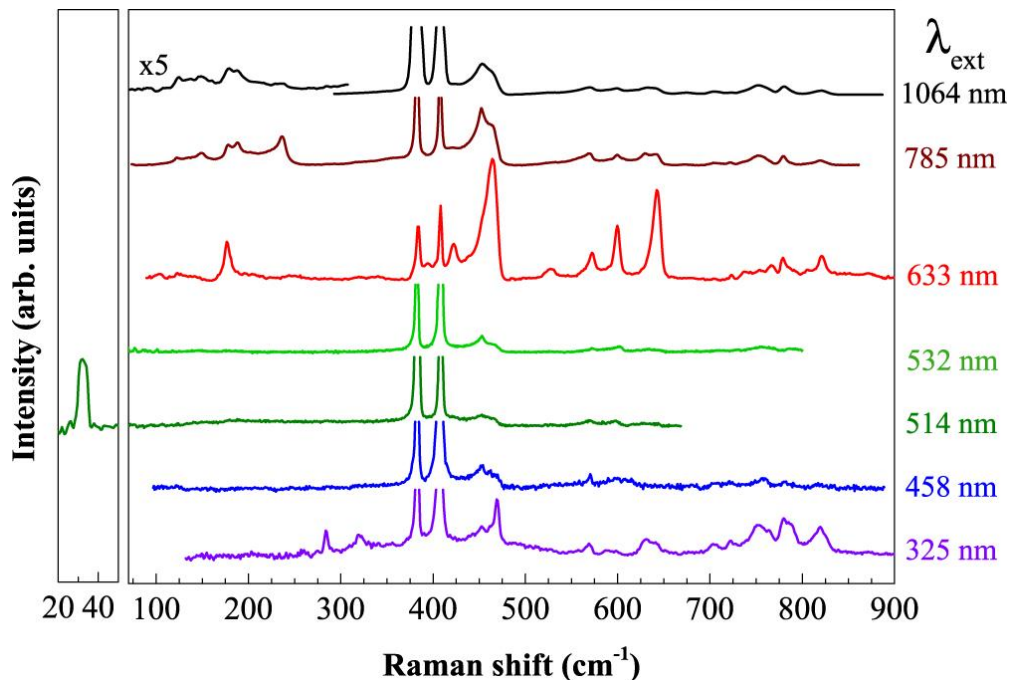
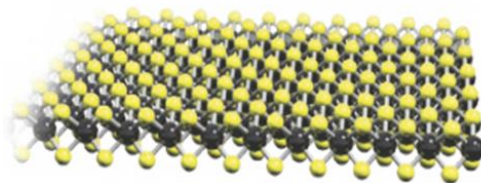
$\lambda_{\text{ext}} \approx E_g \text{ or } E_i$: resonance conditions

Raman intensity:

$$I \propto \frac{2\pi}{\hbar} \left| \frac{\langle 0 | H_{e-r} | n \rangle \langle n | H_{e-ph} | n' \rangle \langle n' | H_{e-r} | 0 \rangle}{(\hbar\omega_i - (E_{|n\rangle} - E_{|0\rangle}) + i\Gamma)(\hbar\omega_s - (E_{|n'\rangle} - E_{|0\rangle}) + i\Gamma)} \right|^2$$

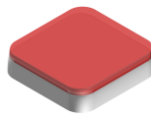


MoS₂
(single crystal)

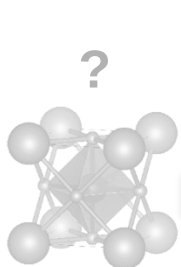


Materials design roadmap: Raman perspective

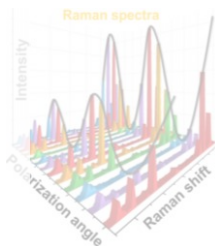
**Reference
Raman studies**



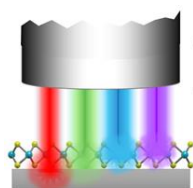
**Applied
Raman studies**



Theory:
Lattice
dynamics
calculations



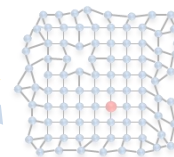
Experiment:
Polarization
Raman
measurements



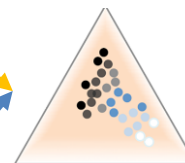
Experiment:
Multiwavelength
excitation Raman
measurements



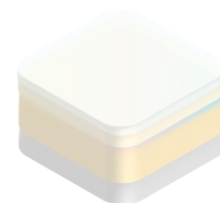
*high crystal quality,
stoichiometric samples*



**Defect
identification**



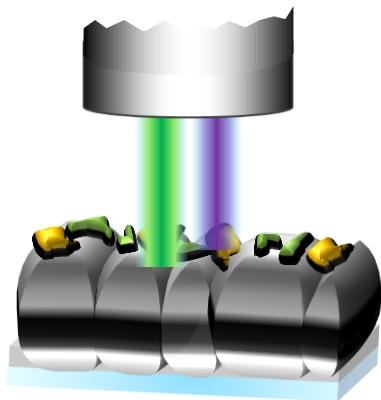
**Secondary phase
identification:**
phase diagram



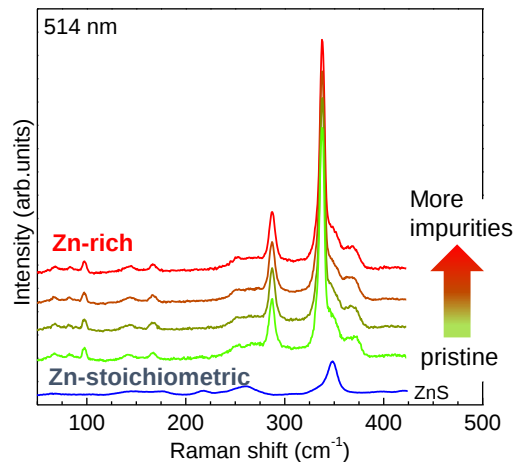
**Structure-function
correlation:**
Device performance

Multiwavelength excitation Raman spectroscopy: impurity identification

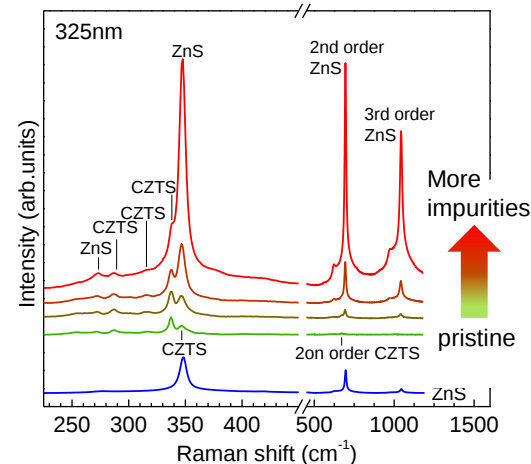
Assessment of ZnS in $\text{Cu}_2\text{ZnSnS}_4$



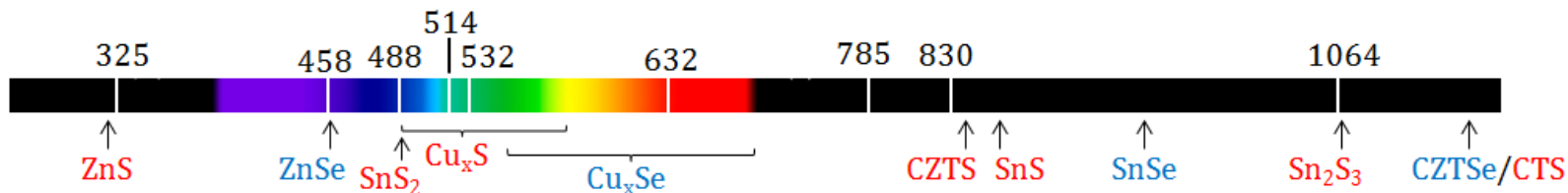
Standard Raman spectroscopy

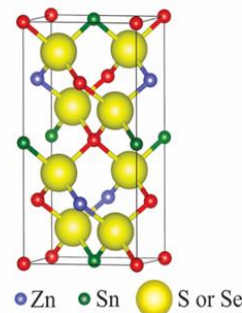


Resonance Raman spectroscopy



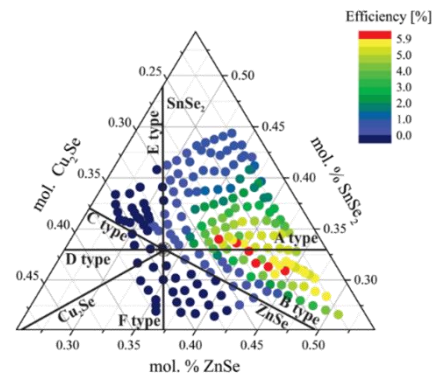
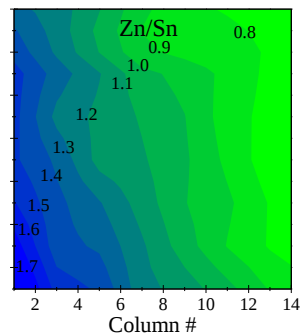
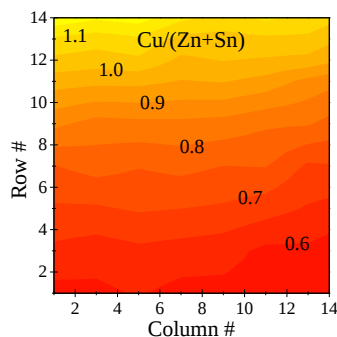
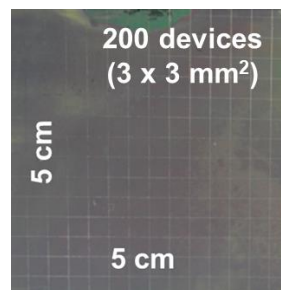
Multiwavelength excitation Raman spectroscopy



Kesterite:
 $\text{Cu}_2\text{ZnSnSe}_4$


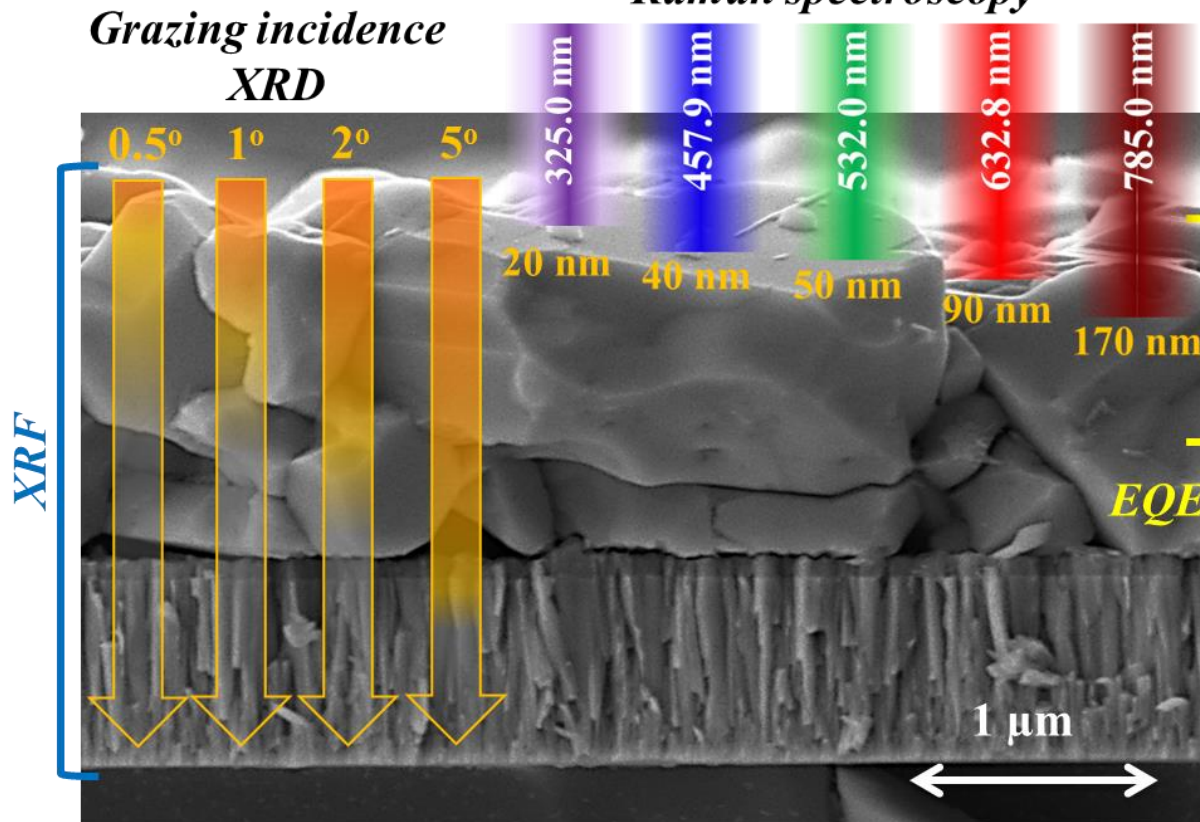
Multiwavelength excitation Raman spectroscopy:

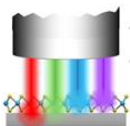
Effect of impurities on the performance of solar cells



Multiwavelength excitation Raman spectroscopy:

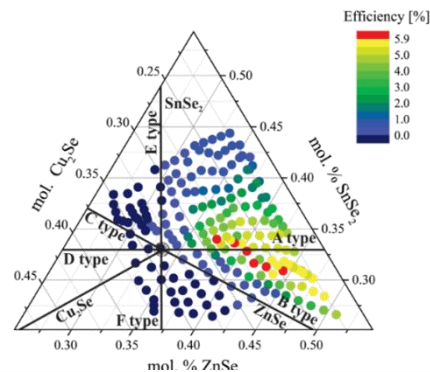
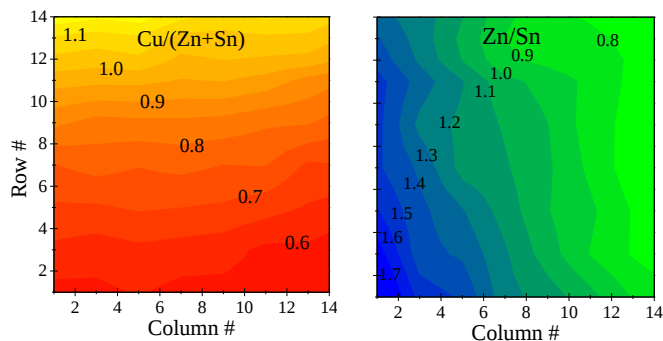
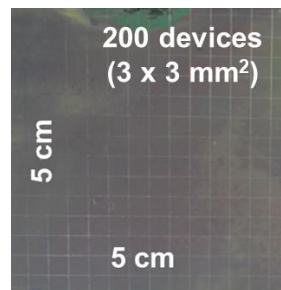
Raman spectroscopy



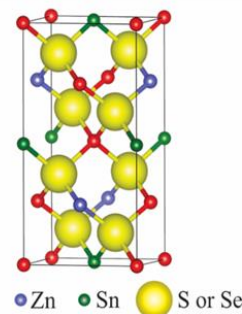


Multiwavelength excitation Raman spectroscopy:

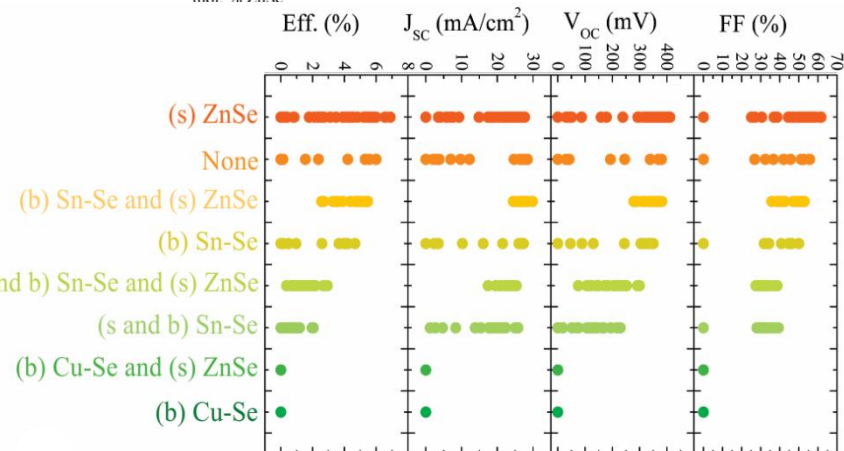
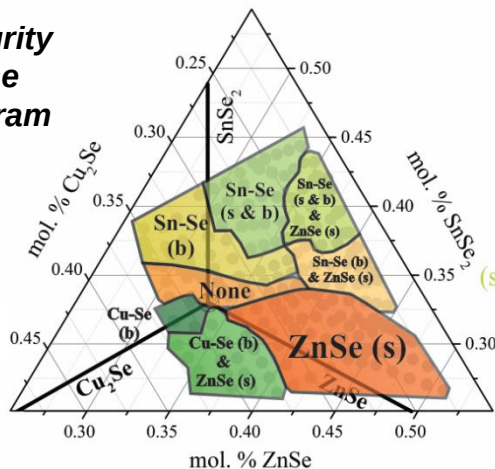
Effect of impurities on the performance of solar cells



Kesterite: $\text{Cu}_2\text{ZnSnSe}_4$

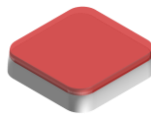


Impurity phase diagram

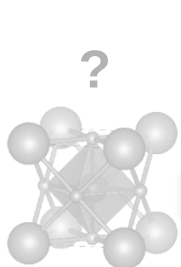


Materials design roadmap: Raman perspective

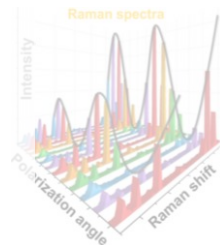
**Reference
Raman studies**



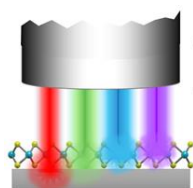
**Applied
Raman studies**



Theory:
Lattice
dynamics
calculations



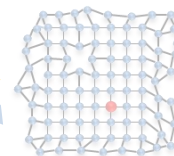
Experiment:
Polarization
Raman
measurements



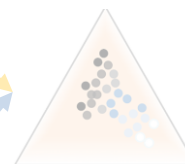
Experiment:
Multiwavelength
excitation Raman
measurements



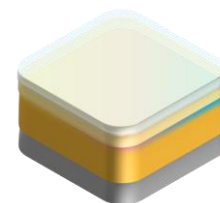
*high crystal quality,
stoichiometric samples*



**Defect
identification**



**Secondary phase
identification:**
phase diagram



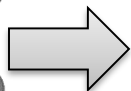
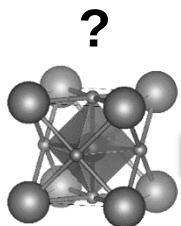
**Structure-function
correlation:**
Device performance

Materials design roadmap: Raman perspective

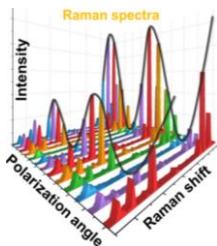
**Reference
Raman studies**



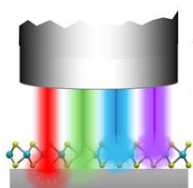
**Applied
Raman studies**



Theory:
Lattice
dynamics
calculations



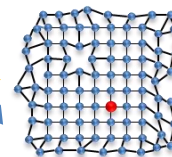
Experiment:
Polarization
Raman
measurements



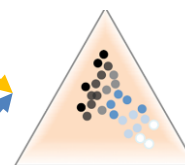
Experiment:
Multiwavelength
excitation Raman
measurements



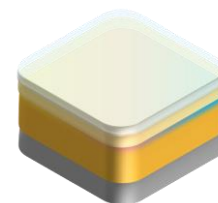
*high crystal quality,
stoichiometric samples*



**Defect
identification**

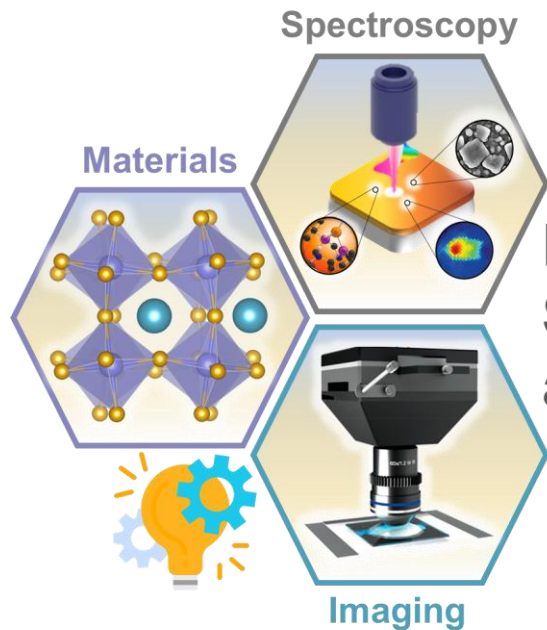


**Secondary phase
identification:**
phase diagram



**Structure-function
correlation:**
Device performance

Thank you for your attention!



Nanomaterials Spectroscopy and Imaging



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